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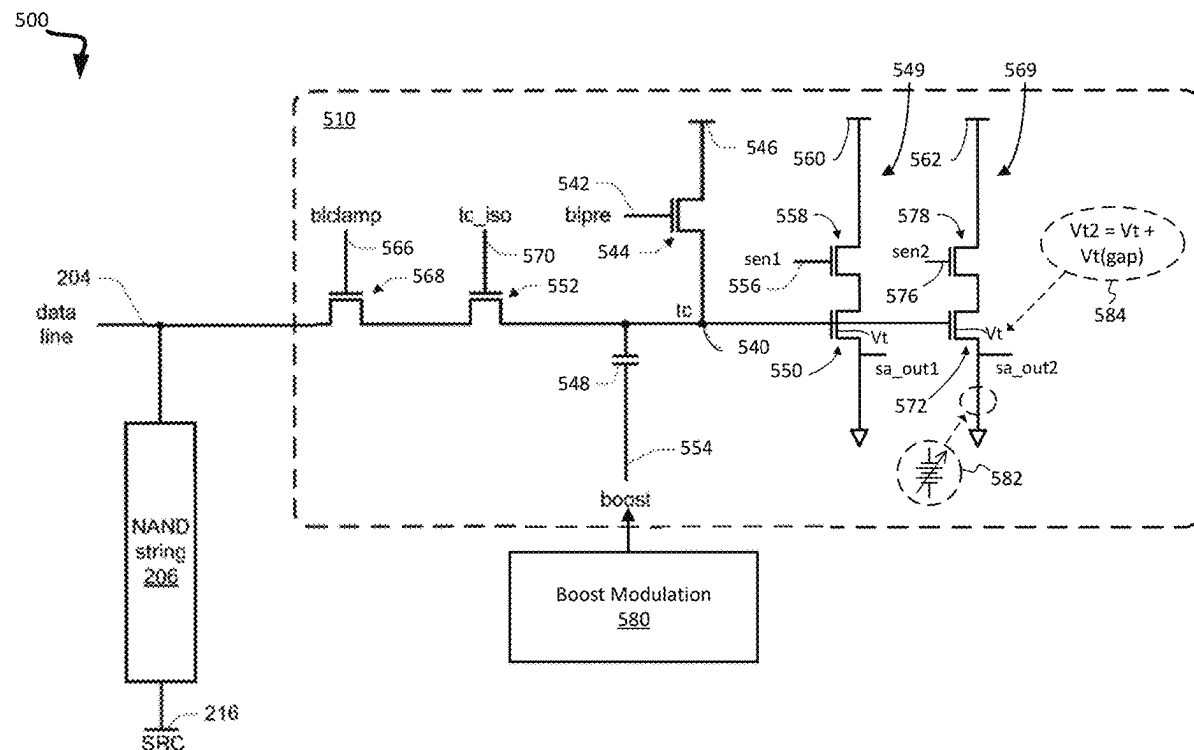
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ABSTRACT

A memory device can include a memory array and control logic, operatively coupled to the memory array, to perform operations including identifying a target cell of the memory array and assigning the target cell to a state information bin. The target cell is associated with a read operation, and the state information bin defines a boost voltage level offset.

Related U.S. Application Data

(63) Continuation of application No. 18/132,489, filed on Apr. 10, 2023, now Pat. No. 12,315,575.



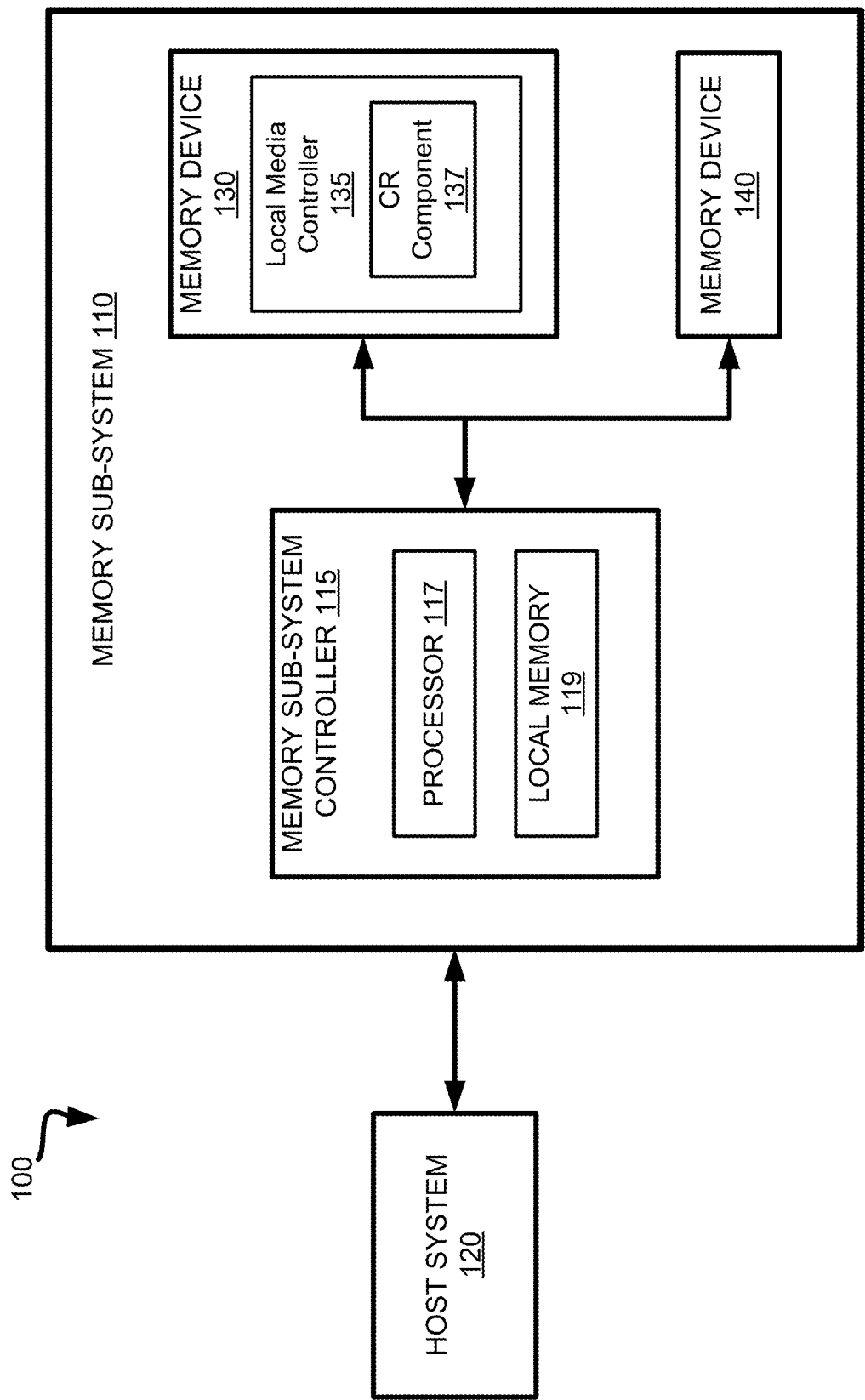


FIG. 1A

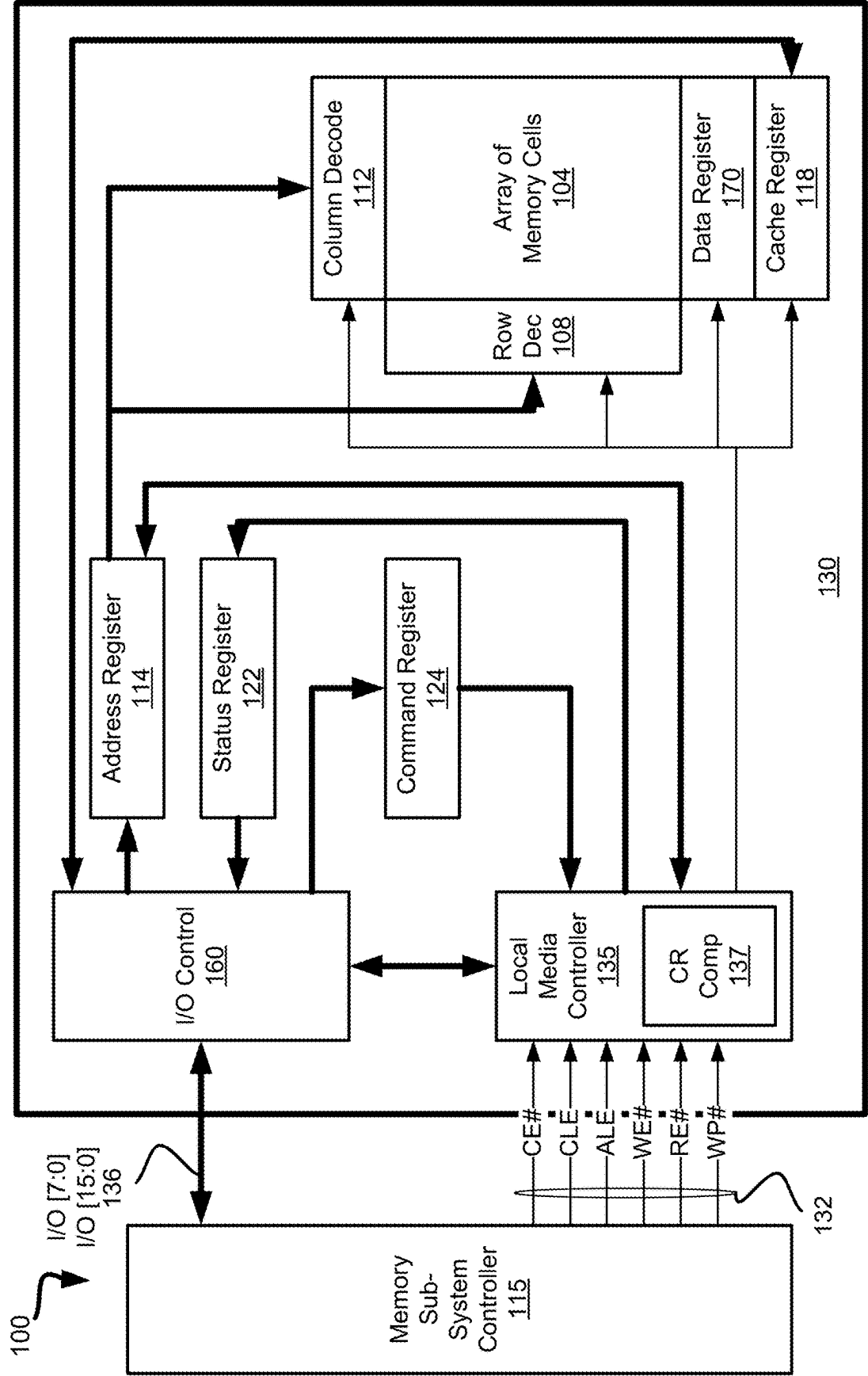


FIG. 1B

200A

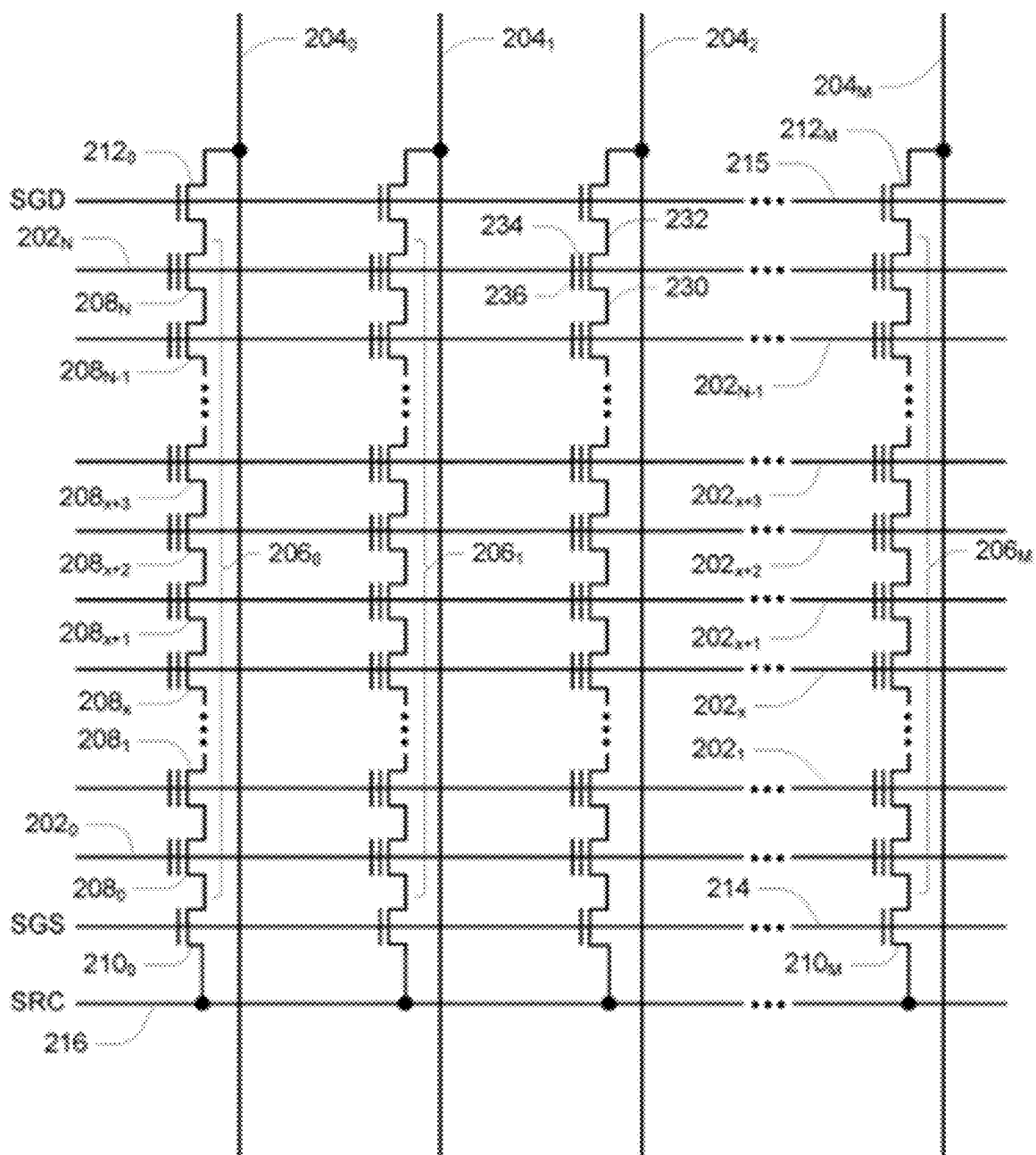


FIG. 2A

200B

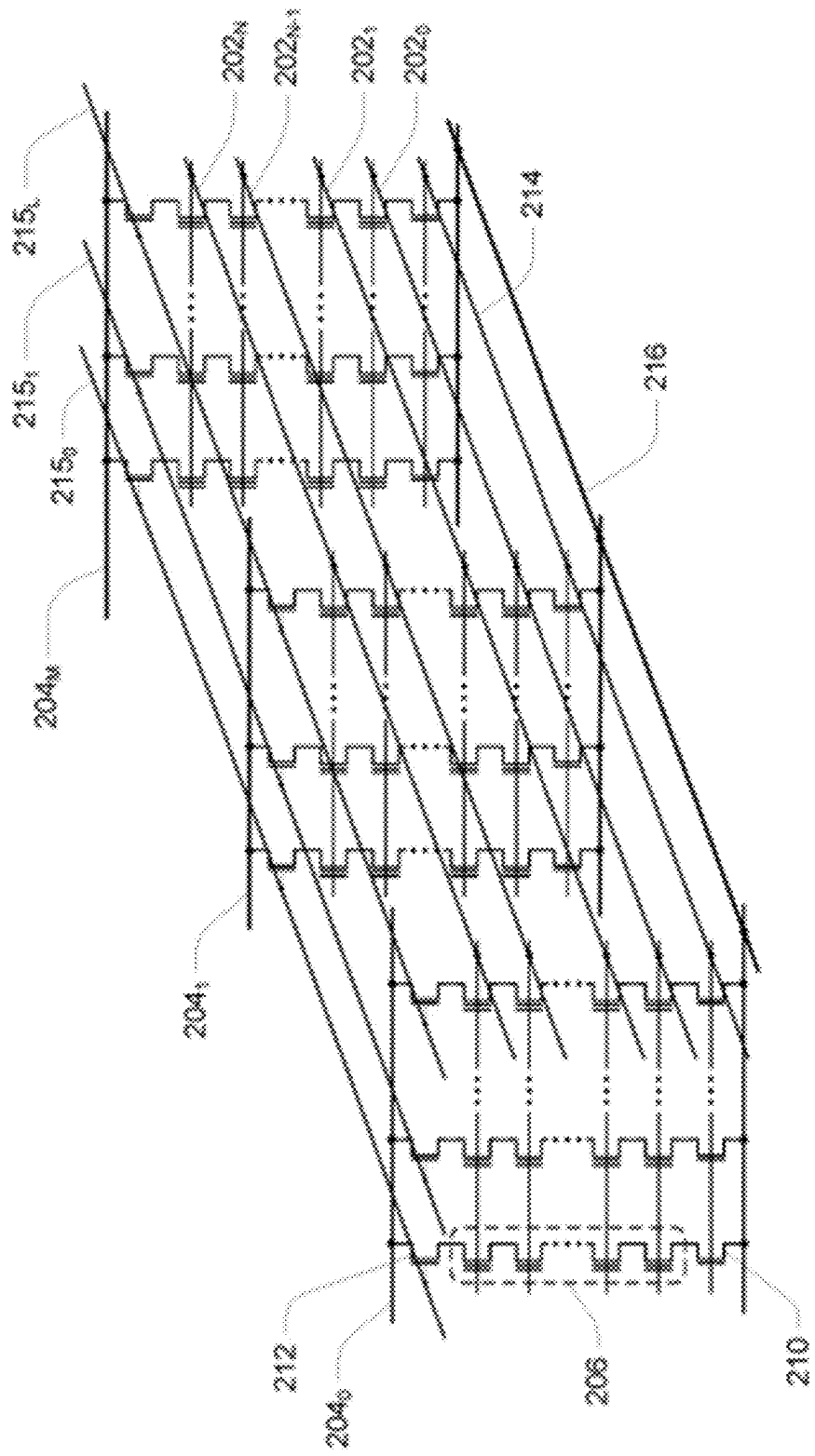


FIG. 2B

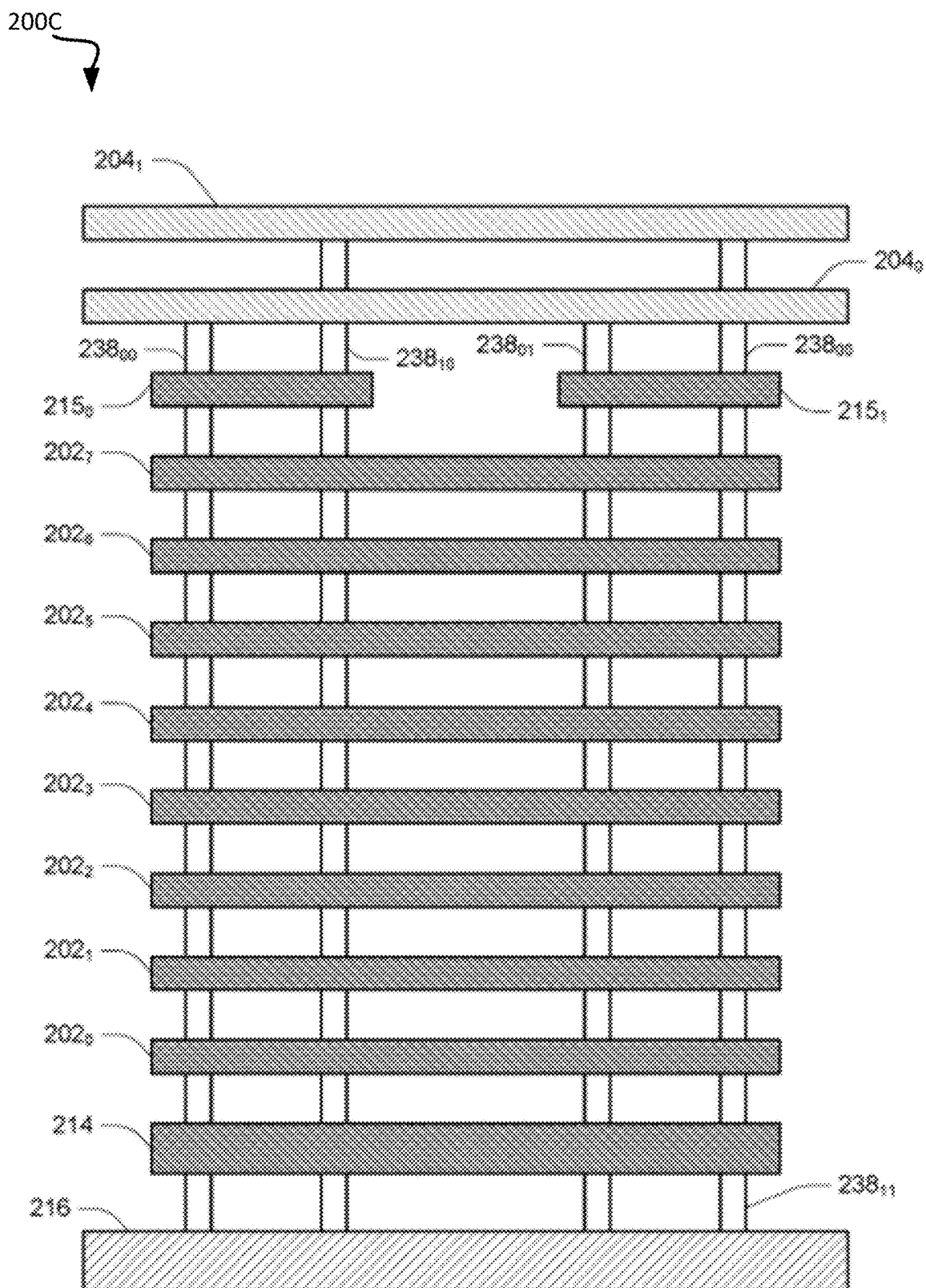


FIG. 2C

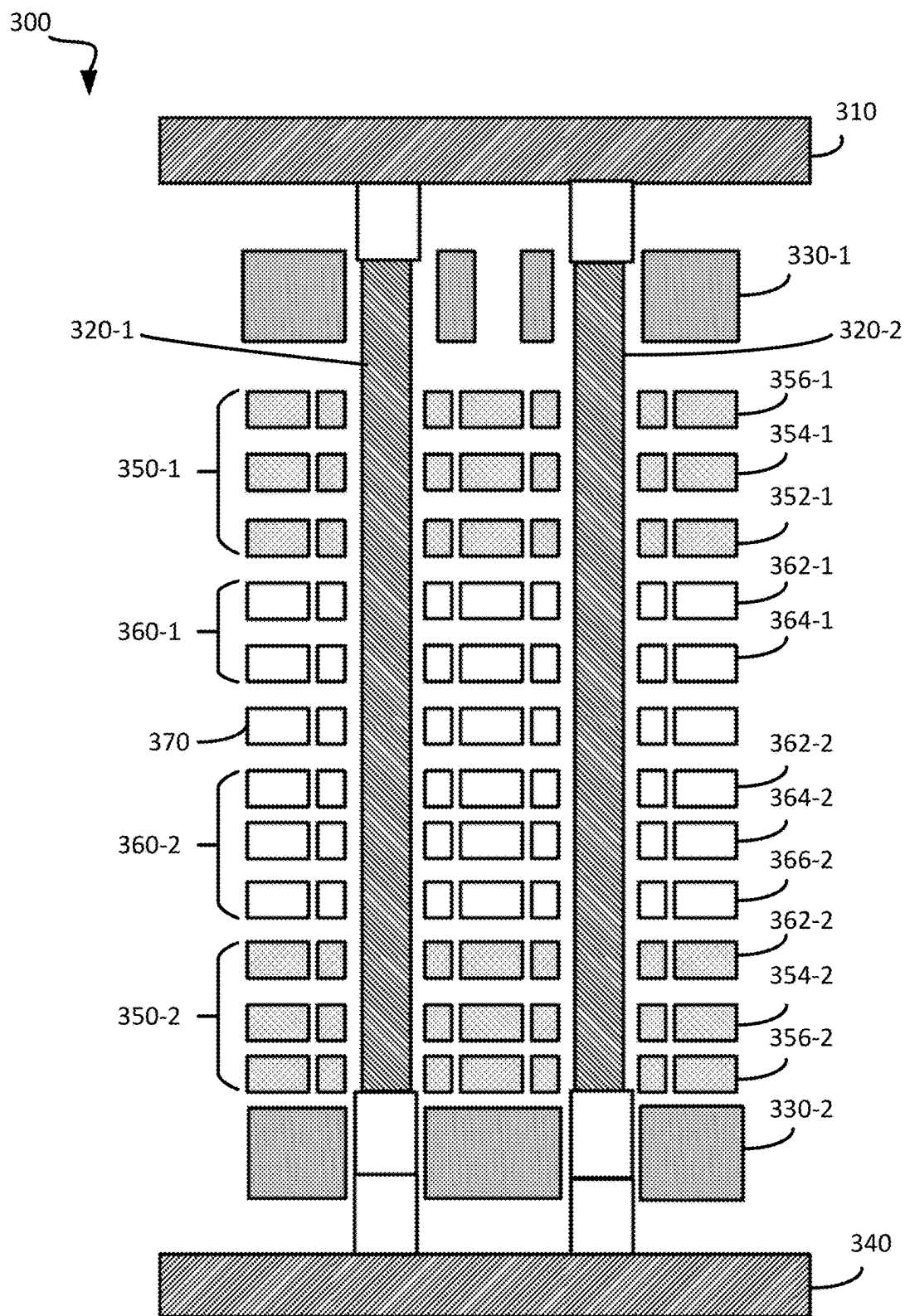


FIG. 3

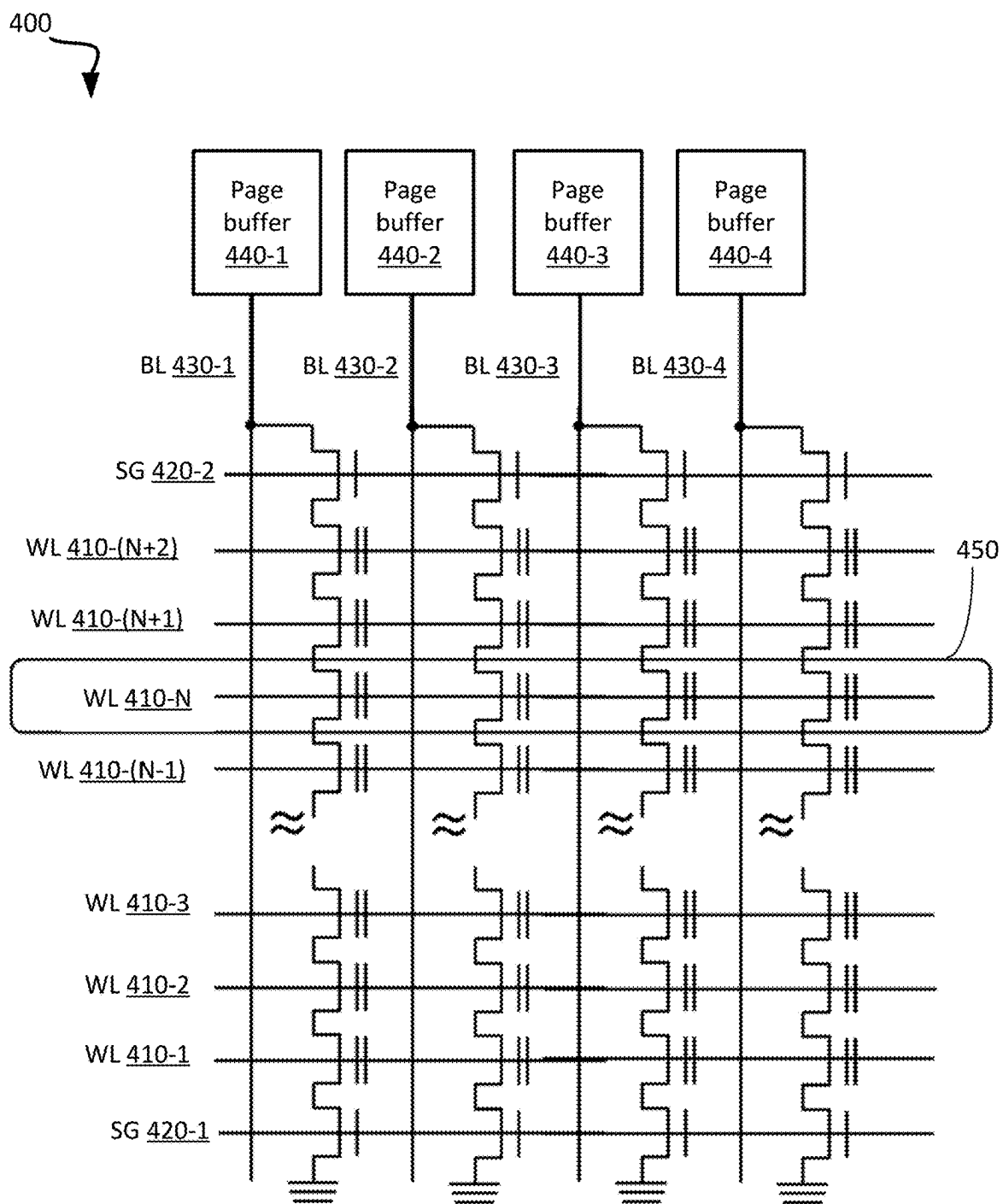


FIG. 4

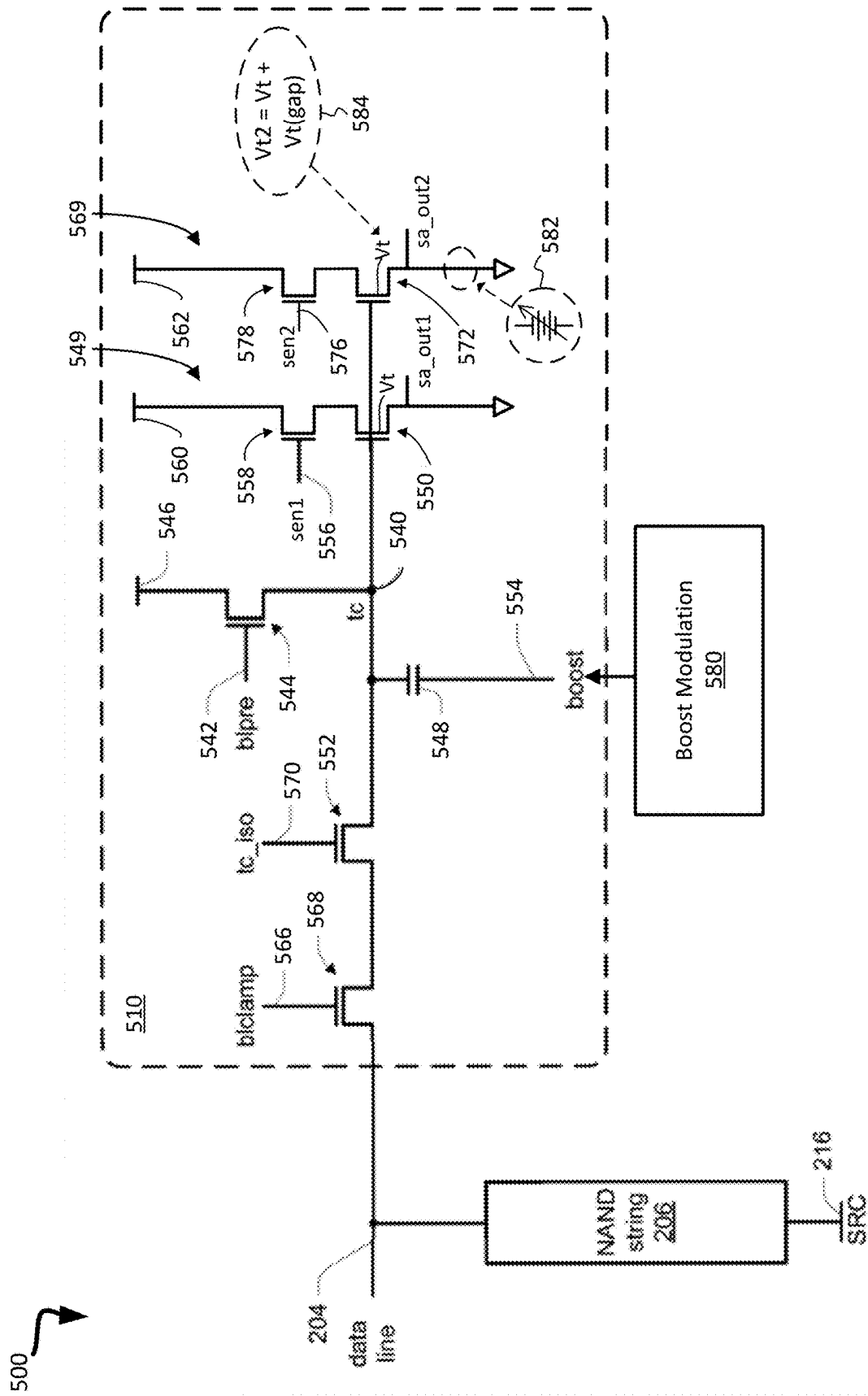


FIG. 5

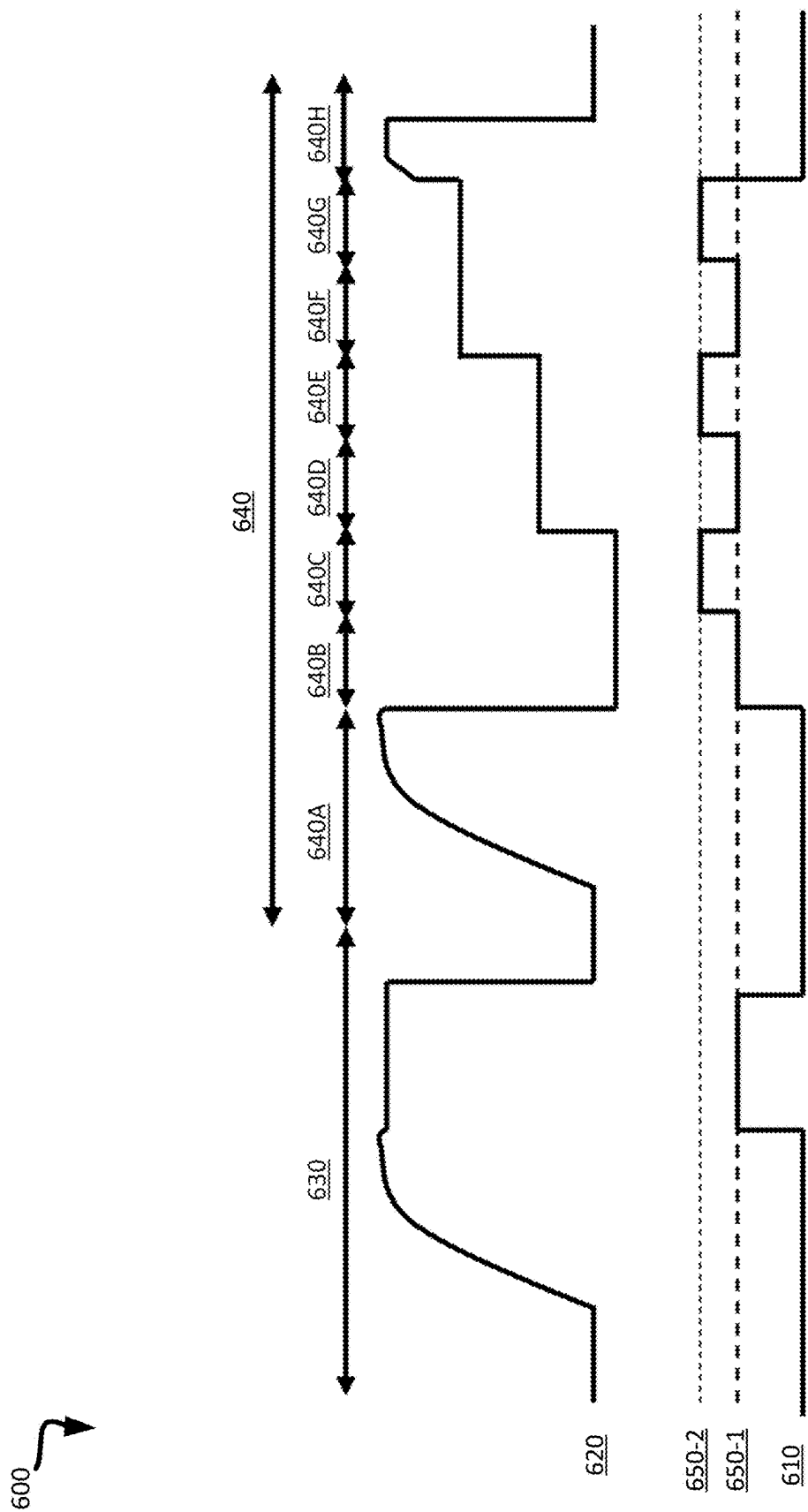


FIG. 6

700

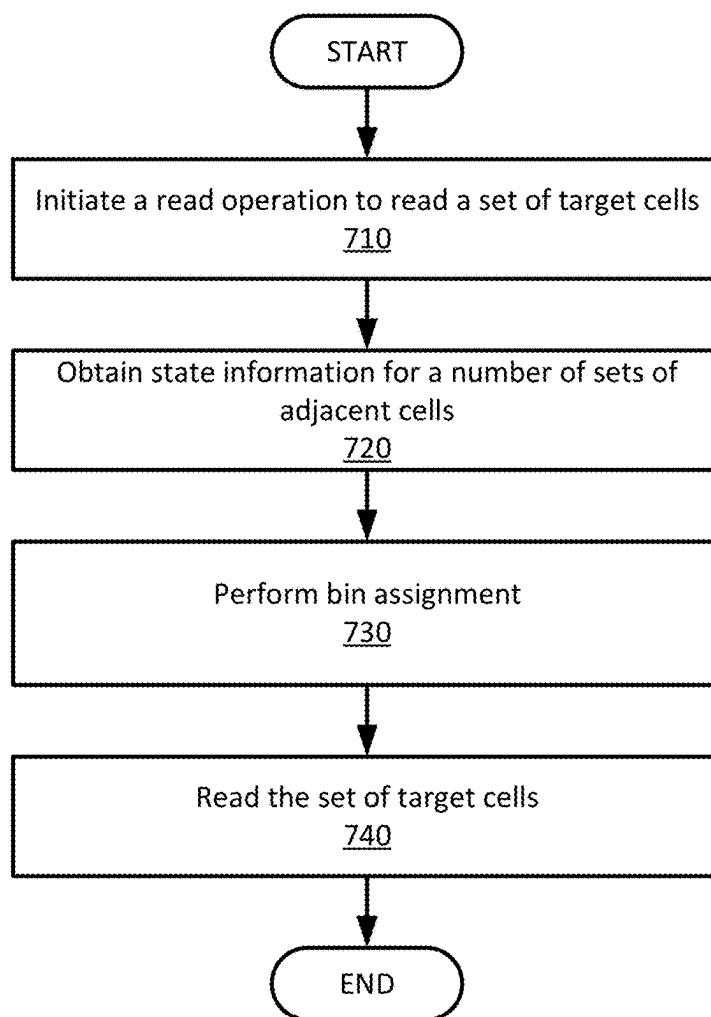


FIG. 7

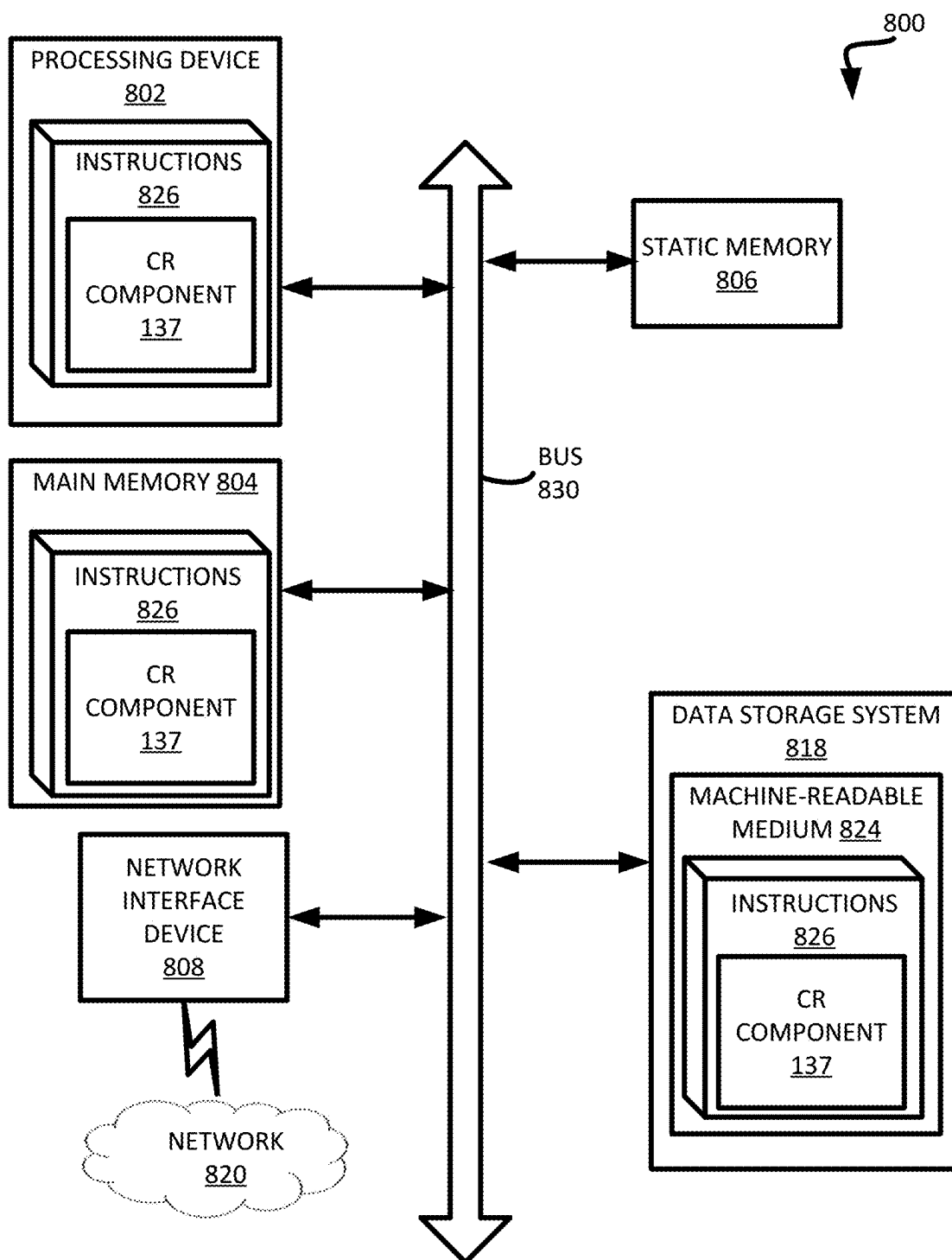


FIG. 8

BOOST VOLTAGE MODULATED CORRECTIVE READ

RELATED APPLICATION

[0001] This application is a continuation of U.S. patent application Ser. No. 18/132,489, filed on Apr. 10, 2023 and entitled “BOOST VOLTAGE MODULATED CORRECTIVE READ”, which claims the benefit of U.S. Provisional Application 63/335,788, filed on Apr. 28, 2022 and entitled “BOOST VOLTAGE MODULATED CORRECTIVE READ”, the entire contents of each of which are incorporated by reference herein.

TECHNICAL FIELD

[0002] Embodiments of the disclosure relate generally to memory sub-systems, and more specifically, relate to boost voltage modulated corrective read.

BACKGROUND

[0003] A memory sub-system can include one or more memory devices that store data. The memory devices can be, for example, non-volatile memory devices and volatile memory devices. In general, a host system can utilize a memory sub-system to store data at the memory devices and to retrieve data from the memory devices.

BRIEF DESCRIPTION OF THE DRAWINGS

[0004] The disclosure will be understood more fully from the detailed description given below and from the accompanying drawings of various embodiments of the disclosure. The drawings, however, should not be taken to limit the disclosure to the specific embodiments, but are for explanation and understanding only.

[0005] FIG. 1A illustrates an example computing system that includes a memory sub-system, in accordance with some embodiments of the present disclosure.

[0006] FIG. 1B is a block diagram of a memory device in communication with a memory sub-system controller of a memory sub-system, in accordance with some embodiments of the present disclosure.

[0007] FIGS. 2A-2C are diagrams of portions of an example array of memory cells included in a memory device, in accordance with some embodiments of the present disclosure.

[0008] FIG. 3 is a diagram of an example three-dimensional (3D) replacement gate memory device that can enable performance of corrective reads implementing incremental reads, in accordance with some embodiments of the present disclosure.

[0009] FIG. 4 is a diagram of a portion of a memory device, in accordance with some embodiments of the present disclosure.

[0010] FIG. 5 is a schematic of circuitry capable of implementing boost voltage modulation, in accordance with some embodiments of the present disclosure.

[0011] FIG. 6 is a timing diagram illustrating an example implementation of boost voltage modulated corrective read, in accordance with some embodiments of the present disclosure.

[0012] FIG. 7 is a flow diagram of an example method to implement boost voltage modulated corrective read, in accordance with some embodiments of the present disclosure.

[0013] FIG. 8 is a block diagram of an example computer system in which embodiments of the present disclosure may operate.

DETAILED DESCRIPTION

[0014] Aspects of the present disclosure are directed to corrective reads implementing boost voltage modulated corrective read. A memory sub-system can be a storage device, a memory module, or a combination of a storage device and memory module. Examples of storage devices and memory modules are described below in conjunction with FIGS. 1A-1B. In general, a host system can utilize a memory sub-system that includes one or more components, such as memory devices that store data. The host system can provide data to be stored at the memory sub-system and can request data to be retrieved from the memory sub-system.

[0015] A memory sub-system can include high density non-volatile memory devices where retention of data is desired when no power is supplied to the memory device. One example of non-volatile memory devices is a negative-and (NAND) memory device. Other examples of non-volatile memory devices are described below in conjunction with FIGS. 1A-1B. A non-volatile memory device is a package of one or more dies. Each die includes one or more planes. For some types of non-volatile memory devices (e.g., NAND devices), each plane includes a set of physical blocks. Each block consists of a set of pages. Each page includes a set of memory cells. A memory cell is an electronic circuit that stores information. Depending on the memory cell type, a memory cell can store one or more bits of binary information, and has various logic states that correlate to the number of bits being stored. The logic states can be represented by binary values, such as “0” and “1”, or combinations of such values.

[0016] A memory device can include multiple memory cells arranged in a two-dimensional or three-dimensional grid. Memory cells are formed onto a silicon wafer in an array of columns and rows. A memory device can further include conductive lines connected to respective ones of the memory cells, referred to as wordlines and bitlines. A wordline can refer to one or more rows of memory cells of the memory device and a bitline can refer to one or more columns of memory cells. The intersection of a bitline and wordline constitutes the address of the memory cell. A block hereinafter refers to a unit of the memory device used to store data and can include a group of memory cells, a wordline group, a wordline, or individual memory cells. One or more blocks can be grouped together to form a plane of the memory device in order to allow concurrent operations to take place on each plane. The memory device can include circuitry that performs concurrent memory page accesses of two or more memory planes. For example, the memory device can include a respective access line driver circuit and power circuit for each plane of the memory device to facilitate concurrent access of pages of two or more memory planes, including different page types.

[0017] Some memory devices can be three-dimensional (3D) memory devices (e.g., 3D NAND devices). For example, a 3D memory device can include memory cells that are placed between sets of layers including a pillar (e.g., polysilicon pillar), a tunnel oxide layer, a charge trap (CT) layer, and a dielectric (e.g. oxide) layer. A 3D memory device can have a “top deck” corresponding to a first side and a “bottom deck” corresponding to a second side. With-

out loss of generality, the first side can be a drain side and the second side can be a source side. For example, a 3D memory device can be a 3D replacement gate memory device having a replacement gate structure using wordline stacking.

[0018] A memory cell (“cell”) can be programmed (written to) by applying a certain voltage to the cell, which results in an electric charge being held by the cell. For example, a voltage signal V_{CG} that can be applied to a control electrode of the cell to open the cell to the flow of electric current across the cell, between a source electrode and a drain electrode. More specifically, for each individual cell (having a charge Q stored thereon) there can be a threshold control gate voltage V_T (also referred to as the “threshold voltage”) such that the source-drain electric current is low for the control gate voltage (V_{CG}) being below the threshold voltage, $V_{CG} < V_T$. The current increases substantially once the control gate voltage has exceeded the threshold voltage, $V_{CG} > V_T$. Because the actual geometry of the electrodes and gates varies from cell to cell, the threshold voltages can be different even for cells implemented on the same die. The cells can, therefore, be characterized by a distribution P of the threshold voltages, $P(Q, V_T) = dW/dV_T$, where dW represents the probability that any given cell has its threshold voltage within the interval $[V_T, V_T + dV_T]$ when charge Q is placed on the cell.

[0019] A memory device can exhibit threshold voltage distributions $P(Q, V_T)$ that are narrow compared with the working range of control voltages tolerated by the cells of the device. Accordingly, multiple non-overlapping distributions $P(Q_k, V_T)$ (“valleys”) can be fit into the working range allowing for storage and reliable detection of multiple values of the charge Q_k , $k=1, 2, 3, \dots$. The distributions (valleys) are interspersed with voltage intervals (“valley margins”) where none (or very few) of the cells of the device have their threshold voltages. Such valley margins can, therefore, be used to separate various charge states Q_k —the logical state of the cell can be determined by detecting, during a read operation, between which two valley margins the respective threshold voltage V_T of the cell resides. Specifically, the read operation can be performed by comparing the measured threshold voltage V_T exhibited by the memory cell to one or more reference voltage levels corresponding to known valley margins (e.g., centers of the margins) of the memory device.

[0020] One type of cell is a single level cell (SLC), which stores 1 bit per cell and defines 2 logical states (“states”) (“1” or “L0”) and “0” or “L1”) each corresponding to a respective V_T level. For example, the “1” state can be an erased state and the “0” state can be a programmed state (L1). Another type of cell is a multi-level cell (MLC), which stores 2 bits per cell (1 bit for upper page (UP) data and 1 bit for lower page (LP) data) and defines 4 states (“11” or “L0”, “10” or “L1”, “01” or “L2” and “00” or “L3”) each corresponding to a respective V_T level. For example, the “11” state can be an erased state and the “01”, “10” and “00” states can each be a respective programmed state. Another type of cell is a triple level cell (TLC), which stores 3 bits per cell (1 bit for UP data, 1 bit for LP data and 1 bit for extra page (XP) data) and defines 8 states (“111” or “L0”, “110” or “L1”, “101” or “L2”, “100” or “L3”, “011” or “L4”, “010” or “L5”, “001” or “L6”, and “000” or “L7”) each corresponding to a respective V_T level. For example, the “111” state can be an erased state and each of the other states

can be a respective programmed state. Another type of a cell is a quad-level cell (QLC), which stores 4 bits per cell (1 bit for UP data, 1 bit for LP data, 1 bit for XP data, and 1 bit for top page (TP) data) and defines 16 states L0-L15, where L0 corresponds to “1111” and L15 corresponds to “0000”. Another type of cell is a penta-level cell (PLC), which stores 5 bits per cell and defines 32 states. Other types of cells are also contemplated. Thus, an n -level cell can use 2^n levels of charge to store n bits of information for n pages. A memory device can include one or more arrays of memory cells such as SLCs, MLCs, TLCs, QLCs, PLCs, etc. or any combination of such. For example, a memory device can include an SLC portion, and an MLC portion, a TLC portion, a QLC portion, or a PLC portion of cells.

[0021] A valley margin can also be referred to as a read window. For example, in a SLC cell, there is 1 read window that exists with respect to the 2 V_T distributions. As another example, in an MLC cell, there are 3 read windows that exist with respect to the 4 V_T distributions. As yet another example, in a TLC cell, there are 7 read windows that exist with respect to the 8 V_T distributions. Read window size generally decreases as the number of states increases. For example, the 1 read window for the SLC cell may be larger than each of the 3 read windows for the MLC cell, and each of the 3 read windows for the MLC cell may be larger than each of the 7 read windows for the TLC cell, etc. Read window budget (RWB) refers to the cumulative value of the read windows.

[0022] Cells of a memory array that are selected to be read during a read operation can be referred to target cells connected to a target wordline. The target cells can neighbor adjacent cells connected to at least one wordline neighboring the target wordline (“adjacent wordline”). For example, the at least one adjacent wordline can be a single wordline neighboring the target wordline or a pair of wordlines neighboring the target wordline. Illustratively, the target wordline can be referred to as an n -th wordline (WL_n), and the at least one adjacent wordline can include at least one of adjacent wordline $n-1$ (WL_{n-1}) or adjacent wordline $n+1$ (WL_{n+1}). For example, in a 3D memory device, the set of adjacent wordlines can include a wordline located directly above the target wordline and/or a wordline located directly below the target wordline.

[0023] Each target cell has a respective group of adjacent cells. Each group of adjacent cells includes at least one cell that neighbors its respective target cell (e.g., one cell connected to WL_{n-1} and/or one cell connected to WL_{n+1}). More specifically, each target cell can be connected to the same bitline as each cell of the respective group of adjacent cells, such that the target cell and the cells of the respective group of adjacent cells are within the same string. Accordingly, each group of adjacent cells can include a single adjacent cell, or a pair of adjacent cells connected to a same bitline as a respective target cell.

[0024] A read can include a prologue phase during which a controller activates voltage pumps (e.g., causes voltage pumps to be turned on) and loads information for the read operation, a strobe phase in which a number of strobes are performed, and an epilogue phase during which the controller causes the cells to discharge, deactivates the voltage pumps (e.g., causes the voltage pumps to be turned off) and causes the memory device to return to an idle or standby state (e.g., depending on the state of the CE #signal). A strobe refers to a read performed at a particular read level

offset. For example, for a 3 strobe page type, a 3 strobe read can be performed during the strobe phase.

[0025] Cell-to-cell interference may exist in a memory array between the target cells and their respective groups of adjacent cells. Cell-to-cell interference can lead to lateral charge migration and V_T distribution shift. Cell-to-cell interference, in addition to intrinsic charge loss, can further lead to a widening of V_T distributions. The V_T distribution widening can cause RWB degradation, which can negatively affect memory device reliability. For example, RWB degradation can lead to an increase in the number of errors (e.g., bit errors) and/or error rate (e.g., bit error rate (BER)).

[0026] One mechanism to compensate for the effects described above is corrective read. Generally, a corrective read operation is performed to read each target cell using an appropriate read level offset that accounts for the cell-to-cell inference, lateral charge migration and/or intrinsic charge loss caused by the respective group of adjacent cells. The read level offset can be applied with respect to a center read level. For example, the center read level can be located within a valley between target cell V_T distributions.

[0027] To implement a corrective read operation, a controller can, for each group of adjacent cells, obtain cell state information for each cell of the group of adjacent cells. The cell state information for a cell reflects the logical level (e.g., L0-Ln, where n is the total number of logical levels supported) of the cell. For example, if a cell is an SLC cell, the cell state information can reflect whether the cell is in the L0 state or the L1 state. As another example, if the cell is a TLC cell, the cell state information can reflect which of the states L0-L7 that the cell is in. The cell state information for a cell can be obtained by identifying the state of the cell.

[0028] To identify the state of the cell, the controller can cause a read voltage to be applied the cell (e.g., gate electrode of the cell) and determine whether the read voltage activates (e.g., turns on) the cell. If the read voltage activates the cell, this indicates that the read voltage is greater than or equal to the V_T of the cell. Additional read voltage(s) may be applied to the cell to determine whether the cell is in a lower state. If the read voltage does not activate the cell, this means that the read voltage is less than the V_T of the cell, and that the cell is in a higher state. Additional read voltage(s) may be applied until the cell is activated. For each group of adjacent cells, the controller can store the cell state information for each cell of the group of adjacent cells in a respective page buffer (e.g., static page buffer). Each page buffer can be connected to a respective group of adjacent cells via a bitline.

[0029] In some embodiments, the cell state information for each cell of a group of adjacent cells is 1-bit information. For example, obtaining the 1-bit cell state information can involve applying a single strobe read to each cell of the group of adjacent cells. A strobe refers to a read performed at a particular read level offset. If the group of adjacent cells includes a single cell (e.g., a cell connected to one of the adjacent wordlines WL_{n-1} and WL_{n+1}), then the stored cell state information is 1 bit in total. The 1 bit stored cell state information can be used to implement 1-bit corrective read (1BCR). If the group of adjacent cells includes a pair of cells (e.g., cells connected to the adjacent wordlines WL_{n-1} and WL_{n+1}), then the stored cell state information is 2 bits in total. The 2 bit stored cell state information can be used to implement a “1-bit 2-sided” version of 2-bit corrective read (2BCR).

[0030] In some embodiments, the cell state information for each cell of a group of adjacent cells is 2-bit information. For example, obtaining the 2-bit cell state information can involve applying a three strobe read to each cell of the group of adjacent cells. If the group of adjacent cells includes a single adjacent cell (e.g., a cell connected to one of the adjacent wordlines WL_{n-1} and WL_{n+1}), then the stored cell state information is 2 bits in total. The 2 bit stored cell state information can be used to implement a “2-bit 1-sided” version of 2BCR. If the group of adjacent cells includes a pair of cells (e.g., cells connected to the adjacent wordlines WL_{n-1} and WL_{n+1}), then the stored cell state information is 4 bits in total. The 4 bit stored cell state information can be used to implement 4-bit corrective read (4BCR).

[0031] The controller can then assign each target cell to a respective state information bin (“bin”) using the cell state information for each cell of the respective group of adjacent cells. As will be described in further detail below, each bin defines a respective cell state information condition, and a target cell is assigned to a bin if the cell(s) within its respective group of adjacent cells satisfy the cell state information condition for the bin. Thus, the bins divide each target cell V_T distribution into a number of respective target cell V_T sub-distributions, where each target cell V_T sub-distribution is formed from the target cells assigned to a respective bin.

[0032] For example, assume that a group of adjacent cells for a target cell connected to WL_n is a single adjacent cell connected to WL_{n-1} or WL_{n+1} . The cell state information condition for a bin can define a range of states for single adjacent cells. A target cell can then be assigned to the bin if the cell state information for the single adjacent cell indicates that the state of the single adjacent cell falls within the range.

[0033] As another example, assume that a group of adjacent cells for a target cell connected to WL_n is a pair of adjacent cells including a first adjacent cell connected to WL_{n-1} and a second adjacent cell connected to WL_{n+1} . The cell state information condition for a bin can define a first range of states for first adjacent cells and a second range of states for second adjacent cells. The target cell can then be assigned to the bin if the cell state information for the first adjacent cell indicates that the state of the first adjacent cell falls within the first range and if the cell state information for the second adjacent cell indicates that the state of the second adjacent cell falls within the second range.

[0034] The number of bins can be determined by the particular corrective read implementation (e.g., 1BCR, 2BCR or 4BCR). More specifically, the number of bins can be determined as 2^B , where B equals the total number of bits of cell state information stored for a group of adjacent cells.

[0035] For example, in a 1BCR implementation in which $B=1$, the number of bins is 2 (i.e., 2) and each bin defines a respective cell state information condition. Illustratively, for a QLC cell implementation in which there are 16 total possible states L0-L15, a target cell can be assigned to a first bin assigned with a first read level offset if its single adjacent cell is determined to have a state from L0-L7, and a target cell can be assigned to a second bin assigned with a second read level offset if its single adjacent cell is determined to have a state from L8-L15.

[0036] As another example, in a 2-bit 1-sided 2BCR implementation in which $B=2$, the number of bins is 4 (i.e., 2^2) and each bin defines a respective cell state information

condition. Illustratively, for the QLC cell implementation, a target cell can be assigned to a first bin assigned with a first read level offset if its single adjacent cell is determined to have a state from L0-L3, a target cell can be assigned to a second bin if its single adjacent cell is determined to have a state from L4-L7, a target cell can be assigned to a third bin if its single adjacent cell is determined to have a state from L8-L11, and a target cell can be assigned to a fourth bin if its single adjacent cell is determined to have a state from L12-L15.

[0037] As yet another example, in a 1-bit 2-sided 2BCR implementation in which $B=2$, the number of bins is 4 (i.e., 2^2) and each bin defines a respective cell state information condition. Illustratively, for the QLC cell implementation, a target cell can be assigned to a first bin if the adjacent cell connected to adjacent wordline WL_{n-1} and the adjacent cell connected to adjacent wordline WL_{n+1} are each determined to have a state from L0-L7. A target cell can be assigned to a second bin if the adjacent cell connected to adjacent wordline WL_{n-1} is determined to have a state from L0-L7 and the adjacent cell connected to adjacent wordline WL_{n+1} is determined to have a state from L8-L15. A target cell can be assigned to a third bin if the adjacent cell connected to adjacent wordline WL_{n-1} is determined to have a state from L8-L15 and the adjacent cell connected to adjacent wordline WL_{n+1} is determined to have a state from L0-L7. A target cell can be assigned to a fourth bin if the adjacent cell connected to adjacent wordline WL_{n-1} and the adjacent cell connected to adjacent wordline WL_{n+1} are each determined to have a state from L8-L15.

[0038] As yet another example, in a 4BCR implementation in which $B=4$, the number of bins is 16 (i.e., 2^4) and each bin defines a respective cell state information condition. Illustratively, for the QLC cell implementation, a target cell can be assigned to a first bin if the adjacent cell connected to adjacent wordline WL_{n-1} and the adjacent cell connected to adjacent wordline WL_{n+1} each have a state from L0-L3. A target cell can be assigned to a second bin if the adjacent cell connected to adjacent wordline WL_{n-1} is determined to have a state from L0-L3 and the adjacent cell connected to adjacent wordline WL_{n+1} is determined to have a state from L4-L7. A target cell can be assigned to a third bin if the adjacent cell connected to adjacent wordline WL_{n-1} is determined to have a state L0-L3 and the adjacent cell connected to adjacent wordline WL_{n+1} is determined to have a state from L8-L11. A target cell can be assigned to a fourth bin if the adjacent cell connected to adjacent wordline WL_{n-1} is determined to have a state from L0-L3 and the adjacent cell connected to adjacent wordline WL_{n+1} is determined to have a state from L12-L15. The remaining bins can be generated with other similar combinations of states.

[0039] Each bin is assigned a respective read level offset for reading the target cells assigned to the bin. Each read level offset accounts for the effect that the state of each cell of the group of adjacent cells has on the respective target cell. Typically, the read level offset assigned to a bin is empirically determined through observation or experimentation of the effect that adjacent cell(s) with varying states have on respective target cells. The bin assignments and corresponding read level offsets can be stored in a metadata area of the device. Accordingly, the bins and read level offset assignments can be pre-determined before assigning target cells to bins.

[0040] The controller can then cause the target cells to be read using respective ones of the read level offsets. For example, the controller can cause target cells of a first bin, which form a first target cell V_T sub-distribution, to be read at a first read level. The first read level is determined by locating a center read level, and applying the read level offset assigned to the first bin to the center read level. The center read level can have a voltage magnitude located within the valley between a pair of target cell V_T distributions, and the read level offset can adjust the center read level such that the first read level can have a voltage magnitude located in the valley to the left of the first target cell V_T sub-distribution. The other target cells can be read similarly.

[0041] In view of the above, the total number of reads performed can be equal to the number of bins or target cell V_T sub-distributions. For example, in a 1BCR implementation, the target cells of the first bin can be read using the first read level offset and the target cells of the second bin can be read using the second read level offset as described above, for a total of 2 reads. As another example, in a 2BCR implementation (e.g., 1-bit 2-sided or 2-bit 1-sided), the target cells in each of the four bins can be read using a respective read level offset, for a total of 4 reads. As yet another example, in a 4BCR implementation, the target cells in each of the sixteen bins can be read using a respective read level offset, for a total of 16 reads.

[0042] As described above, 4BCR can be implemented by reading sixteen bins of target cells each with a respective read level offset. During each of the 16 reads, a number of page reads are performed. For example, to read a QLC target cell, LP could be read 4 times, UP could be read 4 times, TP could be read 4 times, or XP can be read 3 times. This results in an average of 3.75 reads per page. Therefore, the total number of reads that are performed during QLC 4BCR can be about 66 reads (16 read operations multiplied by 3.75 average reads per page on the target cell, in addition to the 3 reads performed on each of the adjacent cells). The potentially large number of reads that are performed during 4BCR can introduce a performance penalty due to the amount of time needed to perform the 16 reads, and can impact memory device reliability due to phenomena such as read disturb. These negative impacts of corrective read can be amplified for higher bit corrective read implementations, which can require even more target cell reads. Accordingly, reducing the number of reads performed during corrective read can improve memory device performance and reliability.

[0043] Aspects of the present disclosure address the above and other deficiencies by implementing boost voltage modulated corrective read (BMCR), in contrast to the wordline voltage modulated corrective read operations typically used to implement corrective read. In some memory sub-systems, a local media controller can cause a sense circuit within a page buffer used to access the cell(s) of a memory array to perform a read on a memory cell using a number of boost regulators. A boost regulator, or step-up regulator, is a controller or converter that steps up voltage from its input to its output. The boost regulators can provide different boost voltages to capacitively charge the voltage at a sense node of the sense circuit that is coupled to a data line. For example, a voltage clamp can be used to set a pre-charge voltage at a sense node. The sense node can be electrically

connected to a bitline via a switch, and another voltage clamp can set a voltage on the bitline, to enable decay of the voltage at the sense node.

[0044] A first boost voltage can bring the sense node to an initial sense node voltage, and each subsequent boost voltage can slightly vary the sense node voltage. In some memory sub-systems, two separate sensing operations use a total of five different boost voltage levels to sense (e.g., attempt to read or verify) a cell via the data line. The sensed voltage levels can be used to generate histogram data reflecting a count of the number of cells that are sensed at a particular voltage level. By analyzing the histogram data, the local media controller can determine local minima. The sense circuit can then use the voltage level associated with the local minima as a boost voltage level for reading data out of the cell (e.g., distinguishing between the two logical states).

[0045] Wordline voltage modulation can be achieved through boost voltage modulation, such that corrective read can be implemented using boost voltage modulation. Such boost voltage modulation may provide a faster way to modulate the read level as compared to wordline voltage modulation. Using boost voltage modulation to achieve wordline voltage modulation may be limited to a particular voltage range in the wordline voltage domain. For example, the voltage range in the wordline voltage domain can be defined from about -70 mV to about 100 mV.

[0046] In contrast to wordline modulated corrective read, which reads the set of target cells on a bin-by-bin basis, BMCR can read the set of target cells on a strobe-by-strobe basis. For example, reading of the set of target cells across all bins can start with a prologue phase, as described above. After the prologue phase, each of the bins can be read on a strobe-by-strobe basis. As described above, a strobe refers to a read performed at a particular read level offset. Assume that there are three strobes performed during the strobe phase. A first strobe read can be performed on each bin. After the first strobe reads are applied to the bins, a second strobe read is performed on each bin. After the second strobes are applied to the bins, a third strobe is performed on each bin. Stepping through different bins of each strobe during BMCR can reduce latency as compared to stepping through different strobes of each bin during wordline modulated corrective read.

[0047] One example of BMCR is 1-bit BMCR. During 1-bit BMCR, the set of target cells are divided into two bins, bin 0 and bin 1, based on the cell state information. For example, one of the bins can be a programmed state bin including target cells that neighbor a group of adjacent cells including at least one cell having a programmed state, and the other one of the bins can be an erased state bin including target cells that neighbor a group of adjacent cells in which each cell has an erased state. If there are three strobes, then the first strobe read can be performed on bin 0, followed by the first strobe read being performed on bin 1. Then, the second strobe read can be performed on bin 0, followed by the second strobe read being performed on bin 1. Then, the third strobe read can be performed on bin 0, followed by the third strobe read being performed on bin 1. After the third strobe read is performed on bin 1, the epilogue phase can be performed, as described above.

[0048] Another example of BMCR is 2-bit BMCR. During 2-bit BMCR, the set of target cells are divided into four bins, bin 0 through bin 3, based on the cell state information. For

example, one of the bins can be an erased state bin (similar to the erased state bin described above), and each of the other bins can be a respective programmed state bin). If there are three strobes, then the first strobe read can be performed on bin 0 through bin 3 in respective order. The same process can be done for the second and third strobe reads being performed on bin 0 through bin 3. After the third strobe read is performed on bin 3, the epilogue phase can be performed, as described above. Further details regarding boost voltage modulated corrective read are described herein below with reference to FIGS. 1-5.

[0049] BMCR can enable hard bit and soft bit information to further improve error correction. BMCR can deliver improved error handling latency and mute read disturb related charge gain observed with wordline voltage modulated corrective read. For example, the read latency during 4BCR employing wordline voltage modulated corrective read can be about 2.4 ms in some implementations. In comparison, the read latency during 4BCR employing BMCR can be about 0.6 ms in some implementations (e.g., about a fourfold improvement in read latency). Accordingly, advantages of the present disclosure include, but are not limited to, improved memory device performance and reliability.

[0050] FIG. 1A illustrates an example computing system **100** that includes a memory sub-system **110** in accordance with some embodiments of the present disclosure. The memory sub-system **110** can include media, such as one or more volatile memory devices (e.g., memory device **140**), one or more non-volatile memory devices (e.g., memory device **130**), or a combination of such.

[0051] A memory sub-system **110** can be a storage device, a memory module, or a combination of a storage device and memory module. Examples of a storage device include a solid-state drive (SSD), a flash drive, a universal serial bus (USB) flash drive, an embedded Multi-Media Controller (eMMC) drive, a Universal Flash Storage (UFS) drive, a secure digital (SD) card, and a hard disk drive (HDD). Examples of memory modules include a dual in-line memory module (DIMM), a small outline DIMM (SO-DIMM), and various types of non-volatile dual in-line memory modules (NVDIMMs).

[0052] The computing system **100** can be a computing device such as a desktop computer, laptop computer, network server, mobile device, a vehicle (e.g., airplane, drone, train, automobile, or other conveyance), Internet of Things (IoT) enabled device, embedded computer (e.g., one included in a vehicle, industrial equipment, or a networked commercial device), or such computing device that includes memory and a processing device.

[0053] The computing system **100** can include a host system **120** that is coupled to one or more memory sub-systems **110**. In some embodiments, the host system **120** is coupled to multiple memory sub-systems **110** of different types. FIG. 1A illustrates one example of a host system **120** coupled to one memory sub-system **110**. As used herein, "coupled to" or "coupled with" generally refers to a connection between components, which can be an indirect communicative connection or direct communicative connection (e.g., without intervening components), whether wired or wireless, including connections such as electrical, optical, magnetic, etc.

[0054] The host system **120** can include a processor chip-set and a software stack executed by the processor chip-set.

The processor chipset can include one or more cores, one or more caches, a memory controller (e.g., NVDIMM controller), and a storage protocol controller (e.g., PCIe controller, SATA controller). The host system 120 uses the memory sub-system 110, for example, to write data to the memory sub-system 110 and read data from the memory sub-system 110.

[0055] The host system 120 can be coupled to the memory sub-system 110 via a physical host interface. Examples of a physical host interface include, but are not limited to, a serial advanced technology attachment (SATA) interface, a peripheral component interconnect express (PCIe) interface, universal serial bus (USB) interface, Fibre Channel, Serial Attached SCSI (SAS), a double data rate (DDR) memory bus, Small Computer System Interface (SCSI), a dual in-line memory module (DIMM) interface (e.g., DIMM socket interface that supports Double Data Rate (DDR)), etc. The physical host interface can be used to transmit data between the host system 120 and the memory sub-system 110. The host system 120 can further utilize an NVMe Express (NVMe) interface to access components (e.g., memory devices 130) when the memory sub-system 110 is coupled with the host system 120 by the physical host interface (e.g., PCIe bus). The physical host interface can provide an interface for passing control, address, data, and other signals between the memory sub-system 110 and the host system 120. FIG. 1A illustrates a memory sub-system 110 as an example. In general, the host system 120 can access multiple memory sub-systems via a same communication connection, multiple separate communication connections, and/or a combination of communication connections.

[0056] The memory devices 130, 140 can include any combination of the different types of non-volatile memory devices and/or volatile memory devices. The volatile memory devices (e.g., memory device 140) can be, but are not limited to, random access memory (RAM), such as dynamic random access memory (DRAM) and synchronous dynamic random access memory (SDRAM).

[0057] Some examples of non-volatile memory devices (e.g., memory device 130) include a negative-and (NAND) type flash memory and write-in-place memory, such as a three-dimensional cross-point ("3D cross-point") memory device, which is a cross-point array of non-volatile memory cells. A cross-point array of non-volatile memory cells can perform bit storage based on a change of bulk resistance, in conjunction with a stackable cross-gridded data access array. Additionally, in contrast to many flash-based memories, cross-point non-volatile memory can perform a write in-place operation, where a non-volatile memory cell can be programmed without the non-volatile memory cell being previously erased. NAND type flash memory includes, for example, two-dimensional NAND (2D NAND) and three-dimensional NAND (3D NAND).

[0058] Each of the memory devices 130 can include one or more arrays of memory cells. One type of memory cell, for example, single level memory cells (SLC) can store one bit per memory cell. Other types of memory cells, such as multi-level memory cells (MLCs), triple level memory cells (TLCs), quad-level memory cells (QLCs), and penta-level memory cells (PLCs) can store multiple bits per memory cell. In some embodiments, each of the memory devices 130 can include one or more arrays of memory cells such as SLCs, MLCs, TLCs, QLCs, PLCs or any combination of such. In some embodiments, a particular memory device can

include an SLC portion, and an MLC portion, a TLC portion, a QLC portion, or a PLC portion of memory cells. The memory cells of the memory devices 130 can be grouped as pages that can refer to a logical unit of the memory device used to store data. With some types of memory (e.g., NAND), pages can be grouped to form blocks.

[0059] Although non-volatile memory components such as a 3D cross-point array of non-volatile memory cells and NAND type flash memory (e.g., 2D NAND, 3D NAND) are described, the memory device 130 can be based on any other type of non-volatile memory, such as read-only memory (ROM), phase change memory (PCM), self-selecting memory, other chalcogenide based memories, ferroelectric transistor random-access memory (FeTRAM), ferroelectric random access memory (FeRAM), magneto random access memory (MRAM), Spin Transfer Torque (STT)-MRAM, conductive bridging RAM (CBRAM), resistive random access memory (RRAM), oxide based RRAM (OxRAM), negative-or (NOR) flash memory, or electrically erasable programmable read-only memory (EEPROM).

[0060] A memory sub-system controller 115 (or controller 115 for simplicity) can communicate with the memory devices 130 to perform operations such as reading data, writing data, or erasing data at the memory devices 130 and other such operations. The memory sub-system controller 115 can include hardware such as one or more integrated circuits and/or discrete components, a buffer memory, or a combination thereof. The hardware can include a digital circuitry with dedicated (i.e., hard-coded) logic to perform the operations described herein. The memory sub-system controller 115 can be a microcontroller, special purpose logic circuitry (e.g., a field programmable gate array (FPGA), an application specific integrated circuit (ASIC), etc.), or other suitable processor.

[0061] The memory sub-system controller 115 can include a processing device, which includes one or more processors (e.g., processor 117), configured to execute instructions stored in a local memory 119. In the illustrated example, the local memory 119 of the memory sub-system controller 115 includes an embedded memory configured to store instructions for performing various processes, operations, logic flows, and routines that control operation of the memory sub-system 110, including handling communications between the memory sub-system 110 and the host system 120.

[0062] In some embodiments, the local memory 119 can include memory registers storing memory pointers, fetched data, etc. The local memory 119 can also include read-only memory (ROM) for storing micro-code. While the example memory sub-system 110 in FIG. 1A has been illustrated as including the memory sub-system controller 115, in another embodiment of the present disclosure, a memory sub-system 110 does not include a memory sub-system controller 115, and can instead rely upon external control (e.g., provided by an external host, or by a processor or controller separate from the memory sub-system).

[0063] In general, the memory sub-system controller 115 can receive commands or operations from the host system 120 and can convert the commands or operations into instructions or appropriate commands to achieve the desired access to the memory devices 130. The memory sub-system controller 115 can be responsible for other operations such as wear leveling operations, garbage collection operations, error detection and error-correcting code (ECC) operations,

encryption operations, caching operations, and address translations between a logical address (e.g., a logical block address (LBA), namespace) and a physical address (e.g., physical block address) that are associated with the memory devices **130**. The memory sub-system controller **115** can further include host interface circuitry to communicate with the host system **120** via the physical host interface. The host interface circuitry can convert the commands received from the host system into command instructions to access the memory devices **130** as well as convert responses associated with the memory devices **130** into information for the host system **120**.

[0064] The memory sub-system **110** can also include additional circuitry or components that are not illustrated. In some embodiments, the memory sub-system **110** can include a cache or buffer (e.g., DRAM) and address circuitry (e.g., a row decoder and a column decoder) that can receive an address from the memory sub-system controller **115** and decode the address to access the memory devices **130**.

[0065] In some embodiments, the memory devices **130** include local media controllers **135** that operate in conjunction with memory sub-system controller **115** to execute operations on one or more memory cells of the memory devices **130**. An external controller (e.g., memory sub-system controller **115**) can externally manage the memory device **130** (e.g., perform media management operations on the memory device **130**). In some embodiments, memory sub-system **110** is a managed memory device, which is a raw memory device **130** having control logic (e.g., local controller **132**) on the die and a controller (e.g., memory sub-system controller **115**) for media management within the same memory device package. An example of a managed memory device is a managed NAND (MNAND) device.

[0066] The local media controller **135** can implement a corrective read (CR) component **137** that can perform boost voltage modulated CR (BMCR). The CR component **137** can initiate a read operation with respect to a set of target cells connected to a target wordline. For example, the CR component **137** can initiate the read operation in response to receiving a request (e.g., read command) via the memory sub-system controller **115** to read the set of target cells.

[0067] The CR component **137** can then obtain, for each target cell, cell state information for from each cell of a respective group of adjacent cells. In some embodiments, each group of adjacent cells includes a single cell. In some embodiments, each group of adjacent cells includes a pair of cells. For example, if the memory device **130** is a 3D memory device, the group of adjacent cells can include a cell directly located above its target cell and and/or a cell located directly below its target cell. Each cell of the group of adjacent cells is connected to a respective wordline of a group of adjacent wordlines neighboring the target wordline. For example, if the memory device **130** is a 3D memory device, the group of adjacent wordlines can include a wordline located directly above the target wordline and/or a wordline located directly below the target wordline.

[0068] In some embodiments, the cell state information for each cell of the group of adjacent cells includes 1-bit cell state information. In some embodiments, the cell state information for each cell of the group of adjacent cells includes 2-bit cell state information. The cell state information for each group of adjacent cells can be stored in a respective page buffer. Each page buffer can be connected to its respective group of adjacent cells and respective target

cell via a respective bitline. In some embodiments, the cell state information for a cell of a group of adjacent cells is a V_T indicative of a state of the cell.

[0069] The CR component **137** can then assign each target cell to a respective state information bin (“bin”) based on the cell state information. Each bin defines a respective cell state information condition, and a target cell is assigned to a bin if the cell(s) within its respective group of adjacent cells satisfy the cell state information condition for the bin. Thus, the bins divide each target cell V_T distribution into a number of respective target cell V_T sub-distributions, where each target cell V_T sub-distribution is formed from the target cells assigned to a respective bin.

[0070] In some embodiments, the cell state information for each group of adjacent cells includes 1-bit information (e.g., the group of adjacent cells includes a single cell having associated 1-bit information) and the set of bins includes two bins. In some embodiments, the cell state information includes 2-bit information (e.g., the group of adjacent cells includes a single cell having associated 2-bit information, or the group of adjacent cells includes a pair of cells each having associated 1-bit information) and the set of bins includes four bins. In some embodiments, the cell state information includes 4-bit information (e.g., the group of adjacent cells includes a pair of cells each having associated 2-bit information) and the set of bins includes sixteen bins.

[0071] Each bin defines a respective boost voltage level offset for modulating a boost voltage. Each boost voltage level offset can be empirically determined prior to implementing the read operation, as being a boost voltage level offset that optimizes reads performed on target cells assigned to the respective bin. For example, each boost voltage level offset can be predefined for each bin. The CR component **137** can then cause each target cell of the set of target cells to be read by modulating the boost voltage using a respective boost voltage level offset. Modulating the boost voltage can include boosting and/or deboosting the boost voltage level in accordance with the boost voltage level offset. The set of target cells can be read on a strobe-by-strobe basis. For example, a number of strobe reads can be performed with respect to each bin of the set of bins. Illustratively, a first strobe read can be performed with respect to each bin of the set of bins. Then, after performing the first strobe read, a second strobe read can be performed with respect to each bin of the set of bins. In some embodiments, three strobe reads are performed with respect to each bin of the set of bins. Further details regarding the operations of the CR component **137** will be described below with reference to FIGS. 4-7.

[0072] FIG. 1B is a simplified block diagram of a first apparatus, in the form of a memory device **130**, in communication with a second apparatus, in the form of a memory sub-system controller **115** of a memory sub-system (e.g., memory sub-system **110** of FIG. 1A), according to an embodiment. Some examples of electronic systems include personal computers, personal digital assistants (PDAs), digital cameras, digital media players, digital recorders, games, appliances, vehicles, wireless devices, mobile telephones and the like. The memory sub-system controller **115** (e.g., a controller external to the memory device **130**), may be a memory controller or other external host device.

[0073] Memory device **130** includes an array of memory cells **104** logically arranged in rows and columns. Memory cells of a logical row are connected to the same access line

(e.g., a wordline) while memory cells of a logical column are selectively connected to the same data line (e.g., a bitline). A single access line may be associated with more than one logical row of memory cells and a single data line may be associated with more than one logical column. Memory cells (not shown in FIG. 1B) of at least a portion of array of memory cells 104 are capable of being programmed to one of at least two target data states.

[0074] Row decode circuitry 108 and column decode circuitry 112 are provided to decode address signals. Address signals are received and decoded to access the array of memory cells 104. Memory device 130 also includes input/output (I/O) control circuitry 160 to manage input of commands, addresses and data to the memory device 130 as well as output of data and status information from the memory device 130. An address register 114 is in communication with I/O control circuitry 160 and row decode circuitry 108 and column decode circuitry 112 to latch the address signals prior to decoding. A command register 124 is in communication with I/O control circuitry 160 and local media controller 135 to latch incoming commands.

[0075] A controller (e.g., the local media controller 135 internal to the memory device 130) controls access to the array of memory cells 104 in response to the commands and generates status information for the external memory sub-system controller 115, i.e., the local media controller 135 is configured to perform access operations (e.g., read operations, programming operations and/or erase operations) on the array of memory cells 104. The local media controller 135 is in communication with row decode circuitry 108 and column decode circuitry 112 to control the row decode circuitry 108 and column decode circuitry 112 in response to the addresses. In one embodiment, local media controller 135 includes the CR component 137, which can implement the defect detection described herein during an erase operation on memory device 130.

[0076] The local media controller 135 is also in communication with a cache register 118. Cache register 118 latches data, either incoming or outgoing, as directed by the local media controller 135 to temporarily store data while the array of memory cells 104 is busy writing or reading, respectively, other data. During a program operation (e.g., write operation), data may be passed from the cache register 118 to the data register 170 for transfer to the array of memory cells 104; then new data may be latched in the cache register 118 from the I/O control circuitry 160. During a read operation, data may be passed from the cache register 118 to the I/O control circuitry 160 for output to the memory sub-system controller 115; then new data may be passed from the data register 170 to the cache register 118. The cache register 118 and/or the data register 170 may form (e.g., may form a portion of) a page buffer of the memory device 130. A page buffer may further include sensing devices (not shown in FIG. 1B) to sense a data state of a memory cell of the array of memory cells 204, e.g., by sensing a state of a data line connected to that memory cell. A status register 122 may be in communication with I/O control circuitry 160 and the local media controller 135 to latch the status information for output to the memory sub-system controller 115.

[0077] Memory device 130 receives control signals at the memory sub-system controller 115 from the local media controller 135 over a control link 132. For example, the control signals can include a chip enable signal CE #, a

command latch enable signal CLE, an address latch enable signal ALE, a write enable signal WE #, a read enable signal RE #, and a write protect signal WP #. Additional or alternative control signals (not shown) may be further received over control link 132 depending upon the nature of the memory device 130. In one embodiment, memory device 130 receives command signals (which represent commands), address signals (which represent addresses), and data signals (which represent data) from the memory sub-system controller 115 over a multiplexed input/output (I/O) bus 136 and outputs data to the memory sub-system controller 115 over I/O bus 136.

[0078] For example, the commands may be received over input/output (I/O) pins [7:0] of I/O bus 136 at I/O control circuitry 160 and may then be written into command register 124. The addresses may be received over input/output (I/O) pins [7:0] of I/O bus 136 at I/O control circuitry 160 and may then be written into address register 114. The data may be received over input/output (I/O) pins [7:0] for an 8-bit device or input/output (I/O) pins [15:0] for a 16-bit device at I/O control circuitry 160 and then may be written into cache register 118. The data may be subsequently written into data register 170 for programming the array of memory cells 104.

[0079] In an embodiment, cache register 118 may be omitted, and the data may be written directly into data register 170. Data may also be output over input/output (I/O) pins [7:0] for an 8-bit device or input/output (I/O) pins [15:0] for a 16-bit device. Although reference may be made to I/O pins, they may include any conductive node providing for electrical connection to the memory device 130 by an external device (e.g., the memory sub-system controller 115), such as conductive pads or conductive bumps as are commonly used.

[0080] It will be appreciated by those skilled in the art that additional circuitry and signals can be provided, and that the memory device 130 of FIGS. 1A-1B has been simplified. It should be recognized that the functionality of the various block components described with reference to FIGS. 1A-1B may not necessarily be segregated to distinct components or component portions of an integrated circuit device. For example, a single component or component portion of an integrated circuit device could be adapted to perform the functionality of more than one block component of FIGS. 1A-1B. Alternatively, one or more components or component portions of an integrated circuit device could be combined to perform the functionality of a single block component of FIGS. 1A-1B. Additionally, while specific I/O pins are described in accordance with popular conventions for receipt and output of the various signals, it is noted that other combinations or numbers of I/O pins (or other I/O node structures) may be used in the various embodiments.

[0081] FIGS. 2A-2C are diagrams of portions of an example array of memory cells included in a memory device, in accordance with some embodiments of the present disclosure. For example, FIG. 2A is a schematic of a portion of an array of memory cells 200A as could be used in a memory device (e.g., as a portion of array of memory cells 104). Memory array 200A includes access lines, such as wordlines 202₀ to 202_N, and a data line, such as bitline 204. The wordlines 202 may be connected to global access lines (e.g., global wordlines), not shown in FIG. 2A, in a many-to-one relationship. For some embodiments, memory array 200A may be formed over a semiconductor that, for

example, may be conductively doped to have a conductivity type, such as a p-type conductivity, e.g., to form a p-well, or an n-type conductivity, e.g., to form an n-well.

[0082] Memory array 200A can be arranged in rows each corresponding to a respective wordline 202 and columns each corresponding to a respective bitline 204. Rows of memory cells 208 can be divided into one or more groups of physical pages of memory cells 208, and physical pages of memory cells 208 can include every other memory cell 208 commonly connected to a given wordline 202. For example, memory cells 208 commonly connected to wordline 202_N and selectively connected to even bitlines 204 (e.g., bitlines 204₀, 204₂, 204₄, etc.) may be one physical page of memory cells 208 (e.g., even memory cells) while memory cells 208 commonly connected to wordline 202_N and selectively connected to odd bitlines 204 (e.g., bitlines 204₁, 204₃, 204₅, etc.) may be another physical page of memory cells 208 (e.g., odd memory cells). Although bitlines 204₃-204₅ are not explicitly depicted in FIG. 2A, it is apparent from the figure that the bitlines 204 of the array of memory cells 200A may be numbered consecutively from bitline 204₀ to bitline 204_M. Other groupings of memory cells 208 commonly connected to a given wordline 202 may also define a physical page of memory cells 208. For certain memory devices, all memory cells commonly connected to a given wordline might be deemed a physical page of memory cells. The portion of a physical page of memory cells (which, in some embodiments, could still be the entire row) that is read during a single read operation or programmed during a single programming operation (e.g., an upper or lower page of memory cells) might be deemed a logical page of memory cells. A block of memory cells may include those memory cells that are configured to be erased together, such as all memory cells connected to wordlines 202₀-202_N (e.g., all strings 206 sharing common wordlines 202). Unless expressly distinguished, a reference to a page of memory cells herein refers to the memory cells of a logical page of memory cells.

[0083] Each column can include a string of series-connected memory cells (e.g., non-volatile memory cells), such as one of strings 206₀ to 206_M. Each string 206 can be connected (e.g., selectively connected) to a source line 216 (SRC) and can include memory cells 208₀ to 208_N. The memory cells 208 of each string 206 can be connected in series between a select gate 210, such as one of the select gates 210₀ to 210_M, and a select gate 212, such as one of the select gates 212₀ to 212_M. In some embodiments, the select gates 210₀ to 210_M are source-side select gates (SGS) and the select gates 212₀ to 212_M are drain-side select gates. Select gates 210₀ to 210_M can be connected to a select line 214 (e.g., source-side select line) and select gates 212₀ to 212_M can be connected to a select line 215 (e.g., drain-side select line). The select gates 210 and 212 might represent a plurality of select gates connected in series, with each select gate in series configured to receive a same or independent control signal. A source of each select gate 210 can be connected to SRC 216, and a drain of each select gate 210 can be connected to a memory cell 208₀ of the corresponding string 206. Therefore, each select gate 210 can be configured to selectively connect a corresponding string 206 to SRC 216. A control gate of each select gate 210 can be connected to select line 214. The drain of each select gate 212 can be connected to the bitline 204 for the corresponding string 206. The source of each select gate 212 can be connected to

a memory cell 208_N of the corresponding string 206. Therefore, each select gate 212 might be configured to selectively connect a corresponding string 206 to the bitline 204. A control gate of each select gate 212 can be connected to select line 215.

[0084] In some embodiments, and as will be described in further detail below with reference to FIG. 2B, the memory array in FIG. 2A is a three-dimensional memory array, in which the strings 206 extend substantially perpendicular to a plane containing SRC 216 and to a plane containing a plurality of bitlines 204 that can be substantially parallel to the plane containing SRC 216.

[0085] FIG. 2B is another schematic of a portion of an array of memory cells 200B (e.g., a portion of the array of memory cells 104) arranged in a three-dimensional memory array structure. The three-dimensional memory array 200B may incorporate vertical structures which may include semiconductor pillars where a portion of a pillar may act as a channel region of the memory cells of strings 206. The strings 206 may be each selectively connected to a bit line 204₀-204_M by a select gate 212 and to the SRC 216 by a select gate 210. Multiple strings 206 can be selectively connected to the same bitline 204. Subsets of strings 206 can be connected to their respective bitlines 204 by biasing the select lines 215₀-215_L to selectively activate particular select gates 212 each between a string 206 and a bitline 204. The select gates 210 can be activated by biasing the select line 214. Each wordline 202 may be connected to multiple rows of memory cells of the memory array 200B. Rows of memory cells that are commonly connected to each other by a particular wordline 202 may collectively be referred to as tiers.

[0086] FIG. 2C is a diagram of a portion of an array of memory cells 200C (e.g., a portion of the array of memory cells 104). Channel regions (e.g., semiconductor pillars) 238₀₀ and 238₀₁ represent the channel regions of different strings of series-connected memory cells (e.g., strings 206 of FIGS. 2A-2B) selectively connected to the bitline 204₀. Similarly, channel regions 238₁₀ and 238₁₁ represent the channel regions of different strings of series-connected memory cells (e.g., NAND strings 206 of FIGS. 2A-2B) selectively connected to the bitline 204₁. A memory cell (not depicted in FIG. 2C) may be formed at each intersection of an wordline 202 and a channel region 238, and the memory cells corresponding to a single channel region 238 may collectively form a string of series-connected memory cells (e.g., a string 206 of FIGS. 2A-2B). Additional features might be common in such structures, such as dummy wordlines, segmented channel regions with interposed conductive regions, etc.

[0087] FIG. 3 is a diagram of an example three-dimensional (3D) replacement gate memory device ("device") 300, in accordance with some embodiments of the present disclosure. However, the embodiments described herein can be applied to any suitable memory device. For example, the device 300 can be similar to memory device 130 and/or memory device 140 of FIGS. 1A-1B.

[0088] As shown, the device 300 includes a bitline 310, pillars 320-1 and 320-2, select gates (SGs) 330-1 and 330-2, a source line (SRC) 340, and WL groups 350-1, 350-2, 360-1 and 360-2. More specifically, WL groups 350-1 and 350-2 are dummy WL groups, and WL groups 360-1 and 360-2 are active WL groups. WL group 350-1 includes dummy WLs 352-1 through 356-1, WL group 350-2

includes dummy WLs 352-2 through 356-2, WL group 360-1 includes active WLs 362-1 and 364-1, and WL group 360-2 includes active WLs 362-2, 364-2 and 366-2. However, such an example should not be considered limiting. A dummy WL corresponds to memory cells that do not store data and are included to satisfy processing margins, while an active WL corresponds to memory cells that store data.

[0089] As further shown, a WL 370 is provided. In some embodiments, the device 300 is a multiple deck device, in which WL groups 350-1 and 360-1 are associated with a first deck (e.g., an upper deck) of the device 300 and the WL groups 350-2 and 360-2 are associated with a second deck (e.g., a lower deck) of the device 300, such that the WL 370 corresponds to a dummy WL separating the WL groups 360-1 and 360-2. In other embodiments, the device 300 is a “single deck” device, in which the WL groups 360-1 and 360-2 are not arranged in decks. Here, the WL 370 can be an active WL within one of the WL groups 360-1 or 360-2.

[0090] FIG. 4 is a diagram of a portion of a memory array 400, in accordance with some embodiments. For example, the memory array 400 can be similar to the memory array 104 of FIG. 1B, the memory array 200A of FIG. 2A, the memory array 200B of FIG. 2B and/or the memory array 200C of FIG. 2C. The memory array 400 can include any suitable number of wordlines (WLs). For example, as shown, the memory array 400 includes a number of wordlines WL 410-1 through WL 410-(N+2). Each of the WLs 410-1 through 410-(N+2) is connected to a respective set of cells. Each of the WLs 410-1 through 410-(N+2) is adjacent to at least one WL. For example, WL 410-(N+1) and WL 410-(N-1) are each adjacent wordlines with respect to WL 410-N. The memory array 400 further includes select gate (SG) 420-1 and SG 420-2. In some embodiments, SG 420-1 is a source-side SG (SGS) and SG 420-2 is a drain-side SG (SGD).

[0091] The memory array 400 further includes a number of bitlines (BLs) including BL 430-1 through 430-4 and a number of page buffers including page buffers 440-1 through 440-4. Each of the page buffers is connected to a respective one of the bitlines. Although only 4 bitlines 430-1 through 430-4 and page buffers 440-1 through 440-4 are shown, the memory array 400 can include any suitable number of bitlines and page buffers.

[0092] In this illustrative example, a set of target cells 450 is selected to be read. The set of target cells 450 includes a number of cells of the target wordline WL 410-N. Each target cell of the set of target cells 450 is adjacent to a pair of adjacent cells. More specifically, the pair of adjacent cells for a particular target cell includes the cell connected to WL 410-(N+1) that is directly above the target cell, and the cell connected to WL 410-(N-1) that is directly below the target cell. That is, a target cell of the set of target cells 450 is connected to a same one of the bitlines as its respective pair of adjacent cells.

[0093] A local media controller (e.g., local media controller 135 of FIGS. 1A-1B) can perform BMCR with respect to the set of target cells 450. To perform BMCR with respect to the set of target cells 450, the local media controller can, for each target cell of the set of target cells 450, cause cell state information to be obtained for each cell of the respective group of adjacent cells. The cell state information for each cell can include a V_T value indicative of the state of the cell (e.g., program state or erase state). For each cell of a

group of adjacent cells, the cell state information can include a V_T value indicative of a state of the cell.

[0094] In some embodiments, the cell state information for each group of adjacent cells is 1-bit information. For example, if each group of adjacent cells includes a single cell (e.g., a cell of WL 410-(N-1) or a cell of WL 410-(N+1)), then the cell state information for each group of adjacent cells can be 1-bit information obtained from the single cell. The local media controller can divide the set of target cells 450 into two bins. Each bin can be assigned target cells connected to an adjacent cell having 1-bit information determined to fall within a respective range of values. For example, assume that the 1-bit information for the single adjacent cell can fall into either a range A or a range B. Thus, each range defines a respective bin, namely bin A and bin B.

[0095] In some embodiments, the cell state information for each group of adjacent cells is 2-bit information. For example, if each group of adjacent cells includes a single cell (e.g., a cell of WL 410-(N-1) or a cell of WL 410-(N+1)), then the cell state information for each group of adjacent cells can be 2-bit information obtained from the single cell. The local media controller can divide the set of target cells 450 into four bins. Each bin can be assigned target cells connected to a group of adjacent cells having 2-bit information determined to fall within a respective range of values. For example, assume that the 2-bit information for a single cell can fall into range A, range B, range C or range D. Thus, each range defines a respective bin, namely bin A, bin B, bin C, bin D.

[0096] As another example, if each group of adjacent cells includes a pair of cells (e.g., a cell of WL 410-(N-1) and a cell of WL 410-(N+1)), then the cell state information for each group of adjacent cells can be 1-bit information obtained from each cell of the pair of cells. The local media controller can divide the set of target cells 450 into four bins. Each bin can be assigned target cells connected to a pair of adjacent cells having 2-bit information determined to fall within a respective combination of ranges of 1-bit information values. For example, assume that the 1-bit information for the cell of WL 410-(N-1) can fall into either a range A or a range B. Further assume that the 1-bit information for the cell of WL 410-(N+1) can fall into either a range 1 or a range 2. Thus, each combination of ranges defines a respective bin, namely bin A1, bin B1, bin A2, and bin B2.

[0097] In some embodiments, the cell state information for each group of adjacent cells is 4-bit information. For example, if each group of adjacent cells includes a pair of cells (e.g., a cell of WL 410-(N-1) or a cell of WL 410-(N+1)), then the cell state information for each group of cells can include 2-bit information obtained each cell of the pair of cells. The local media controller can divide the set of target cells 450 into sixteen bins. Each bin can be assigned target cells connected to a pair of adjacent cells having 4-bit information determined to fall within a respective combination of ranges of 2-bit information values. For example, assume that the 2-bit information for the cell of WL 410-(N-1) can fall into a range A, range B, range C or range D. Further assume that the 2-bit information for the cell of WL 410-(N+1) can fall into a range 1, a range 2, a range 3 or a range 4. Thus, each combination of ranges defines a respective bin, namely bin A1, bin B1, . . . , bin C4 and bin D4.

[0098] Each bin defines a respective boost voltage level offset for modulating a boost voltage. As describe above with reference to FIG. 1A and as will be described in further

detail below with reference to FIGS. 6-7, the local media controller can then cause each target cell of the set of target cells 450 to be read by modulating the boost voltage using a respective boost voltage level offset. The set of target cells 450 can be read on a strobe-by-strobe basis.

[0099] FIG. 5 is a schematic of circuitry 500 capable of implementing boost voltage modulation, in accordance with some embodiments of the present disclosure. As shown, the circuitry 500 includes a sense circuit 500. The sense circuit 500 can facilitate performing a sense operation (e.g., read and/or verify) on a target cell in the memory device. In one embodiment, the sense circuit 500 is, or is a part of, a page buffer, as previously discussed. The sense circuit 500 is illustrated connected to a particular NAND string 206 by a particular data line 204, such as illustrated in more detail in FIG. 2A, for example. Note that select gate transistors 210 and 212 selectively connecting the NAND string 206 to the source 216 and data line 204, respectively, are not shown in FIG. 5. While the discussion is directed to use of the sense circuit 500 with a NAND string 206, other memory structures and architectures are suitable for use with sense circuit 500 where a current path can be selectively created from the data line 204 to the source 216 dependent upon a data state of the target cell selected for sensing.

[0100] As part of a sense operation, the sense circuit 500 can boost (e.g., pre-charge) a sense node (e.g., tc node) 540 by activating a boost transistor 544 (e.g., n-type field effect transistor, or nFET). The boost transistor 544 can be activated by biasing (e.g., driving) the signal line 542 to a particular voltage level (e.g., a voltage level of control signal “blpre”) to activate the boost transistor 544. Control signals of the sense circuit 500 can be provided by the internal controller (e.g., the local media controller 135) of the memory device 130. Such control signals (e.g., both voltage levels and timing) can be defined by the sense operation and are distinguished from signals generated in response to performing the sense operation (e.g., the output signal sa_out1 and sa_out2 or a voltage level generated on the sense node 540). A sense operation can be a read operation, e.g., for providing data output from the array of memory cells, or a verify operation, e.g., for verifying whether a programming pulse successfully changed a threshold voltage of a target memory cell to indicate its desired data state.

[0101] In some embodiments, the boost transistor 544 is connected between a voltage node 546 and the sense node 540. The voltage node 546 can receive a supply voltage, e.g., Vcc. In some embodiments, voltage node 546 can be a variable voltage node. A capacitor 548 coupled with the sense node 540 can be representative of capacitance at the sense node 540 and at additional circuitry connected to it, e.g., the transistors 544, 550, 552, and 572. A voltage node 554 (e.g., a variable voltage node) can apply a voltage level to the capacitor 548. This voltage level can induce a change in voltage level on the sense node 540. The change in voltage level on the sense node 540 can boost the sense node 540 to a higher voltage level, such as through capacitive coupling.

[0102] The circuitry 500 further includes boost voltage modulation circuitry 580. The boost voltage modulation circuitry 580 can provide a boost voltage to the voltage node 554. In some embodiments, the boost voltage modulation circuitry 580 includes multiple boost regulators (not shown) operatively coupled to the voltage node 554. For example, a multiplexer (not shown) can be connected between the boost

regulators and the voltage node 554 (e.g., to be coupled with the capacitor 548). A selection line of the multiplexer can be coupled with the local media controller 135 (FIG. 1B), which can therefore control selection of one of the boost regulators for use in pre-charging the capacitor 548 or selectively adjusting the charge of the capacitor 548 after the pre-charging in order to perform sensing operations. The boost voltage modulation circuitry 580 can be integrated within the sense circuit 500, or can be part of a page buffer of which the sense circuit 500 is part.

[0103] Additional transistor paths of the sense circuit 500 facilitate sensing of a voltage level on the sense node 540. In some embodiments, that additional transistor paths can include at least a first sensing path 549 and a second sensing path 569. For example, the first sensing path 549 includes a first select transistor 558 having a gate coupled with a first sense signal line 556, a drain/source coupled with a voltage node 560, and a source/drain coupled with a first sense transistor 550 of the first sensing path 549. The first sense transistor 550 can have a gate coupled to the sense node 540, a drain/source coupled with the source of the first select transistor 558, and a source/drain coupled with ground. Thus, the first sense transistor 550 is configured to be responsive to a voltage level present on the sense node 540. An output (sa_out1) of the first sensing path 549 can be taken at the source of the first sense transistor 550. The first sense signal line 556 can be configured to receive a control signal (“sen1”) that facilitates isolating the first sense transistor 550 from the voltage node 560, which can be configured to receive a supply voltage, e.g., Vcc. In some embodiments, and as shown, the first select transistor 558 and the first sense transistor 550 are n-channel metal oxide semiconductor (NMOS) transistors (e.g., nFETs). In alternative embodiments, the first select transistor 558 and the first sense transistor 550 are p-channel metal oxide semiconductor (PMOS) transistors (e.g., pFETs).

[0104] In some embodiments, the second sensing path 569 includes a second select transistor 578 having a gate coupled with a second sense signal line 576, a drain coupled with a voltage node 562, and a source coupled with a second sense transistor 572 of the second sensing path 569. The second sense transistor 572 can have a gate that is also coupled to the sense node 540, a drain coupled with the source of the second select transistor 578, and a source coupled with ground. Thus, the second sense transistor 572 is configured to be responsive to a voltage level present on the sense node 540. An output (sa_out2) of the second sensing path 569 can be taken at the source of the second sense transistor 572. The second sense signal line 576 can be configured to receive a control signal sen2 that facilitates isolating the second sense transistor 572 from the voltage node 562, which can be configured to receive a supply voltage, e.g., Vcc. In some embodiments, and as shown, the second select transistor 578 and the second sense transistor 572 are NMOS transistors (e.g., nFETs). In some embodiments, second select transistor 578 and the second sense transistor 572 are PMOS transistors (e.g., pFETs).

[0105] To create a threshold voltage gap between the first sensing path 549 and the second sensing path 569, the first sense transistor 550 and the second sense transistor 572 can be manufactured differently (e.g., with a different V_T) or biased to a different trip point (e.g., sense threshold level), as will be explained. The sense circuit 500 can be designed to generate a threshold voltage gap to between 150 and 220

millivolts (mV), for example, between the two sensing paths. In one embodiment, the threshold voltage gap is 180 mV.

[0106] A first trip point and a second trip point of the two sensing paths **549** and **569**, respectively, can generally be dependent upon the respective V_T 's of the first and second sense transistors **550** and **572**. The sense circuit **500** can be configured to have trip points close to the boost voltage level that can be established on the sense node **540** prior to sensing the selected memory cell. The first trip point can be a particular voltage level on the sense node **540** where the first sensing path **549** outputs a first logic level indicative of a first state of the sense node **540** (e.g., when the voltage level of the sense node **540** is equal to or above the first trip point). The second trip point can be a particular voltage level on the sense node where the second sensing path **569** outputs a second logic level indicative of a second state of the sense node **540** (e.g., when the voltage level of the sense node **540** is equal to or above the second trip point). The sense circuit **500** can output a third logic level indicative of a third state of the sense node **540** (e.g., when the voltage level of the sense node **540** is below the first trip point). The sense circuit **500** can output a fourth logic level indicative of a fourth state of the sense node **540** (e.g., when the voltage level of the sense node **540** is below the second trip point of the second sense transistor **572**). The sensed states of the sense node **540** can be used to provide an indication of the data state of the sensed target cell, and provide histogram data to the local media controller **135**.

[0107] In one embodiment, the first sense transistor **550** can have a first V_T (V_{T1}) and the second sense transistor **572** can have a second V_T **584** (e.g., V_{T2}) that differs from V_{T1} by a threshold voltage gap V_{Tgap} ($V_{T2} = V_{T1} + V_{Tgap}$). As this is an optional embodiment, V_{T2} illustrated as second threshold voltage **584** is encircled with a dashed line. To achieve the threshold voltage gap, the first sense transistor **550** can have a different implant dose than the second sense transistor **572** (e.g., a different n-type implant dose or a different p-type implant dose).

[0108] In another embodiment, each of the first sense transistor **550** and the second sense transistor **572** has the same V_T (e.g., the same V_{gs} values within manufacturing tolerances). The second sensing path **569** can further include a voltage source **582** coupled with the source/drain of the second sense transistor **572** to change a trip point of the second sense transistor **572** by the threshold voltage gap. For example, where the source/drain of the first sense transistor **550** is coupled with (or connected to) ground, the source/drain of the second sense transistor **572** is coupled with (or connected to) the voltage source **582**, where the voltage source **582** is coupled with the ground. In one embodiment, the voltage source **582** is a source-ground regulator coupled between the source of the second sense transistor **572** and ground to variably regulate the voltage bias, and thus the trip point, at the source of the second transistor.

[0109] In various embodiments, a sense circuit output line (e.g., sa_out1 and sa_out2) can be connected to additional circuitry (not illustrated) of the memory device **130** configured to respond to the sense circuit **500** as part of a sensing operation. For example, the sense circuit **500** can be a component of the data register **170** of FIG. 1B and its output sa_out1 and sa_out2 can be provided as an input to the cache register **118** for output of the sensed data state from the memory device **130**. The output signal sa_out1 on an output

line can include a signal generated by a latch (e.g., a latch circuit that is not illustrated) which is representative of a logic level, such as a logic 'high' (e.g., represented by V_{cc}) or logic 'low' (e.g., represented by V_{ss}) level indicative of a sensed data state of a selected memory cell of NAND string **206**, for example.

[0110] During a boost portion of a sense operation, the gate of boost transistor **544** can be biased by a voltage level (e.g., of control signal $blpre$) on signal line **542** to boost the sense node **540** by injecting a boost current into the sense node **540**. An additional voltage level (e.g., of control signal $blclamp$) can be applied to signal line **566** to activate transistor **568** (e.g., nFET), and a further voltage level (e.g., of control signal tc_iso) can be applied to signal line **570** to activate transistor **552** (e.g., nFET). Activating transistors **544**, **552**, and **568** can serve to connect the data line **204** to the voltage node **546**, and thus boost the sense node **540** and the data line **204**.

[0111] Following the boosting of the sense node **540** and the data line **204**, a second portion of the sense operation can be performed to detect whether or not the boosted data line **204** and sense node **540** is discharged during the sense operation, thereby determining the data state of the memory cell selected for sensing. Because the sense circuit **500** employs two different sensing paths **549** and **569**, a single sense operation can be performed to detect two different states of the memory cells, e.g., with reference to the first threshold voltage and the different second threshold voltage, or with reference to the same threshold voltages but employing a different trip point of the second sense transistor **572**.

[0112] Following the boosting of the sense node **540** and the data line **204**, the sense node **540** can be isolated from the data line **204**, such as by deactivating the transistor **568** and/or deactivating the transistor **552**. The data line **204** can then be selectively connected to the source line (SRC) **216** depending upon whether the target cell selected for sensing is activated or deactivated in response to a sense voltage applied to its control gate. After the data line **204** is given an opportunity to discharge, if current is flowing through the NAND string **206**, the sense node **540** can again be connected to the data line **204** by activating the transistors **552** and **568**.

[0113] The voltage level of the data line **204** may be lower than the boost voltage level due to current flow through the NAND string **206**. In such cases, the voltage level of the sense node **540** will likewise experience a drop. If the voltage level of the data line **204** remains at the boosted voltage level, such as when the target cell selected for sensing remains deactivated, the voltage level of the sense node **540** can remain at its boosted (or boosted) voltage level. With the transistors **558** and **578** activated and the voltage level of the sense node **540** applied to the control gate of the first and second sense transistors **550** and **572**, the voltage nodes **560** and **562** can be selectively connected to the sense outputs sa_out1 and sa_out2 depending on a voltage level of the sense node **540**. A latch may also be coupled with each of these sense outputs of the sense circuit **500** to keep track of, and provide an output for, the sensing of the voltage level of the sense node **540** with reference the trip points of the first and second sense transistors **550** and **572**. In one embodiment, each of the sense outputs sa_out1 and sa_out2 are coupled to the same latch. In this embodiment, the $sen1$ and $sen2$ signals can be toggled one at a time in order to create a histogram, which will be discussed in

more detail. In another embodiment, a set of latches are employed, one latch to hold sa_out1 and another latch to hold sa_out2. In this embodiment, toggling is unnecessary, and the two states associated with the two sensing paths can be concurrently stored.

[0114] Various embodiments can utilize boosting and deboosting of the sense node 540 during the sense operation. For example, boosting of the sense node 540 (e.g., capacitively coupling a first boost voltage level to the sense node 540) and deboosting of the sense node 540 (e.g., capacitively coupling a second, lower, boost voltage level to the sense node 540) can be used to facilitate a higher overhead. By boosting the sense node 540 prior to the sense node develop time, the voltage level of the sense node 540 can be allowed to develop longer without prematurely indicating current flow of the data line 204. Subsequent deboosting of the sense node 540 after isolation from the NAND string 206 from the data line 204 can permit the voltage level of the sense node 540 to drop below the trip point (e.g., V_T) of the first and second sense transistors 550 and 572 to indicate that current flow was detected. In sequential sensing performed by the sense circuit 500 during one or more sensing operations, the boost voltage can be provided to the voltage node 554 (e.g., to the capacitor 548) using the boost voltage modulation circuitry 580 (e.g., the multiple boost regulators). The multiple boost regulators can also be multiplexed to additional sense circuits in order to perform parallel sensing operations across multiple memory cells.

[0115] Data lines connected to activated memory cells having V_T 's nearer the sense voltage applied to their control gates can be expected to experience lower levels of discharge and higher resulting voltage levels of the sense node 540 than data lines connected to activated memory cells having V_T 's farther from the sense voltage applied to their control gates. Accordingly, sense nodes 540 indicating activation of the target cell at one boost voltage level during deboosting can indicate deactivation of target cell at a different (e.g., higher) boost voltage level during deboosting. This phenomenon can be used to compensate for a sense voltage that is higher or lower than the local minima between two adjacent V_T distributions. Various embodiments can utilize multiple boost voltage levels coupled to the sense node 540 during a single sensing operation to estimate the conditions that can indicate activation of cells each having a V_T below that local minima, and can indicate deactivation of cells each having a V_T above that local minima (e.g., estimating the location of that local minima).

[0116] FIG. 6 is a timing diagram ("diagram") 600 illustrating an example implementation of corrective read, in accordance with some embodiments of the present disclosure. More specifically, the diagram 600 illustrates an example implementation of 1-bit BMCR. However, other BMCR implementations can be similarly performed (e.g., 2-bit BMCR, 4-bit BMCR).

[0117] As shown, the diagram 600 shows a boost voltage waveform 610 and a wordline voltage waveform 620, an adjacent cell read portion 630 and a target cell read portion 640. The adjacent cell read portion 630 identifies two bins, bin 0 and bin 1.

[0118] The target cell read portion 640 begins with a prologue phase 640A. After the prologue phase 640A, the target cell read portion 640 performs a first strobe read with respect to bin 0, strobe read 640B, and a first strobe read with respect to bin 1, strobe read 640C. To perform the first strobe

read 640B, the boost voltage waveform 610 is modulated to a bin 0 voltage 650-1. To perform the first strobe read 640C, the boost voltage waveform 610 is modulated from the bin 0 voltage 650-1 to a bin 1 voltage 660-1.

[0119] The target cell read portion 640 further performs a second strobe read with respect to bin 0, strobe read 640D, and a second strobe read with respect to bin 1, strobe read 640E. To perform the second strobe read 640D, the boost voltage waveform 610 is modulated from the bin 1 voltage 650-2 to the bin 0 voltage 650-1. To perform the second strobe read 640E, the boost voltage waveform 610 is modulated from the bin 0 voltage 650-1 to the bin 1 voltage 650-2.

[0120] The target cell read portion 640 further performs a third strobe read with respect to bin 0, strobe read 640F, and a third strobe read with respect to bin 1, strobe read 640G. To perform the third strobe read 640F, the boost voltage waveform 610 is modulated from the bin 1 voltage 650-2 to the bin 0 voltage 650-1. To perform the third strobe read 640G, the boost voltage waveform 610 is modulated from the bin 0 voltage 650-1 to the bin 1 voltage 650-2. Thus, during BMCR, the boost voltage waveform 610 is modulated to step through bin 0 and bin 1 on a strobe-by-strobe basis. Once the strobe reads are complete, an epilogue phase 640H is performed to end the target cell read portion 640.

[0121] FIG. 7 is a flow diagram of an example method 700 to implement boost voltage modulated corrective read, in accordance with some embodiments of the present disclosure. The method 700 can be performed by processing logic that can include hardware (e.g., processing device, circuitry, dedicated logic, programmable logic, microcode, hardware of a device, integrated circuit, etc.), software (e.g., instructions run or executed on a processing device), or a combination thereof. In some embodiments, the method 700 is performed by the CR component 137 of FIGS. 1A-1B. Although shown in a particular sequence or order, unless otherwise specified, the order of the processes can be modified. Thus, the illustrated embodiments should be understood only as examples, and the illustrated processes can be performed in a different order, and some processes can be performed in parallel. Additionally, one or more processes can be omitted in various embodiments. Thus, not all processes are required in every embodiment. Other process flows are possible.

[0122] At operation 710, a read operation is initiated to read a set of target cells. For example, processing logic can cause the read operation to be initiated with respect to the set of target cells in response to receiving a request to perform the read operation. The request can be a read command received via a memory sub-system controller (e.g., the memory sub-system controller 115 of FIGS. 1A-1B). Each target cell of the set of target cells is connected to a target wordline.

[0123] The read operation can be a boost voltage modulated corrective read (BMCR). In some embodiments, the BMCR is 1-bit BMCR. In some embodiments, the BMCR is 2-bit BMCR. In some embodiments, the BMCR is 4-bit BMCR. However, the BMCR can be any suitable m-bit BMCR in accordance with embodiments described herein.

[0124] At operation 720, cell state information is obtained. For example, the processing logic can cause cell state information to be obtained from respective groups of adjacent cells. Each group of adjacent cells includes at least one cell adjacent to a respective target cell of the set of target cells. Each cell of the group of adjacent cells is connected to

a respective wordline adjacent to the target wordline. Illustratively, each cell of a group of adjacent cells can be directly above or directly below its respective target cell.

[0125] The cell state information of each cell is indicative of a state of the cell. For example, the cell state information for each cell can include a V_T value indicative of the state of the cell. Obtaining the cell state information can further include storing the cell state information for each group of adjacent cells in a respective page buffer connected to the group of adjacent cells via a bitline.

[0126] In some embodiments, each group of adjacent cells includes a single cell. In a 1-bit BMCR implementation, the cell state information for each group of adjacent cells can include 1-bit information obtained from the single cell. In a 2-bit BMCR implementation, the cell state information for each group of adjacent cells can include 2-bit information obtained from the single cell.

[0127] In some embodiments, each group of adjacent cells includes a pair of cells. In a 2-bit BMCR implementation, the cell state information for each group of adjacent cells can include 1-bit information obtained from each cell of the pair of cells. In a 4-bit BMCR implementation, the cell state information for each group of adjacent cells can include 2-bit information obtained from each cell of the pair of the cells.

[0128] At operation 730, a state information bin (“bin”) assignment is performed. For example, the processing logic can, for each target cell of the set of target cells, determine a bin of a set of bins using the cell state information for its respective group of adjacent cells, and assign each target cell of the set of target cells to the respective bin. Each bin defines a respective boost voltage level offset that modulates the boost voltage during the BMCR.

[0129] In a 1-bit BMCR implementation, the set of bins includes two bins. Each bin can be assigned target cells connected to a group of adjacent cells corresponding to a single cell having 1-bit information determined to fall within a respective range of values. For example, assume that the 1-bit information for the single cell can fall into either a range A or a range B. Thus, each range defines a respective bin, namely bin A and bin B.

[0130] In a 2-bit BMCR implementation, the set of bins includes four bins. For example, if each group of adjacent cells includes a single cell, then each bin can be assigned target cells connected to a group of adjacent cells having 2-bit information determined to fall within a respective range of values. Illustratively, assume that the cell state information for each group of adjacent cells can fall into range A, range B, range C or range D. Thus, each range defines a bin, namely bin A, bin B, bin C, bin D.

[0131] As another example, if the group of adjacent cells includes a pair of cells, then each bin can be assigned target cells connected to a group of adjacent cells having 2-bit information determined to fall within a respective combination of ranges of 1-bit information values. Illustratively, assume that the 1-bit information for a first cell of the pair of cells can fall into either a range A or a range B, and that the 1-bit information for a second cell of the pair of cells can fall into either a range 1 or a range 2. Thus, each combination of ranges defines a respective bin, namely bin A1, bin B1, bin A2, and bin B2.

[0132] In a 4-bit BMCR implementation, the set of bins includes sixteen bins. For example, if each group of adjacent cells includes a pair of cells, then each bin can be assigned

target cells connected to a group of adjacent cells having 4-bit information determined to fall within a respective combination of ranges of 2-bit information values. Illustratively, assume that the 2-bit information for a first cell of the pair of cells can fall into a range A, range B, range C or range D, and that the 2-bit information a second cell of the pair of cells can fall into a range 1, a range 2, a range 3 or a range 4. Thus, each combination of ranges defines a bin, namely bin A1, bin B1 . . . bin C4 and bin D4.

[0133] At operation 740, the set of target cells is read. For example, the processing logic can cause the set of target cells to be read by modulating the boost voltage using respective ones of the boost voltage level offsets. The set of target cells can be read on a strobe-by-strobe basis. For example, a strobe read can be performed with respect to each bin in sequential order by modulating the boost voltage in accordance with the boost voltage level offset defined by the bin. Then, another strobe read can be similarly performed with respect to each bin. The BMCR can implement any number of strobes in accordance with the embodiments described herein. For example, if the BMCR implements a 3 strobe read, then a first strobe read can be performed with respect to each bin, followed by a second strobe with respect to each bin, and then a third strobe with respect to each bin. The data obtained after performing the strobes with respect to each bin can be sent back to the memory sub-system controller. Accordingly, the set of target cells can be read on a strobe-by-strobe basis using BMCR, which can reduce read latency as compared to reading the set of target cells on a bin-by-bin basis.

[0134] To illustrate reading the set of wordline cells on a strobe-by-strobe basis using BMCR, assume that 1-bit BMCR is being performed. As described above, two bins can be defined with the 1-bit information (“bin 0” and “bin 1”). After the prologue, a first strobe read can be performed with respect to bin 0 by modulating the boost voltage in accordance with the boost voltage level offset defined for bin 0, and a first strobe read can be performed with respect to bin 1 by modulating the boost voltage in accordance with the boost voltage level offset defined for bin 1. After the first strobe is done, a second strobe read can similarly be performed with respect to bin 0 and bin 1. After the second strobe is done, then a third strobe read can similarly be performed with respect to bin 0 and bin 1. The data obtained from the strobe reads performed with respect to each of the bins 0 and 1 can be combined to obtain final read data that is sent back to the memory sub-system controller.

[0135] A similar process can be performed for 2-bit BMCR. For example, as described above, four bins can be defined with the 2-bit information (“bin 0” through “bin 3”). A first strobe read can be performed with respect to bins 0 through 3. Then, a second strobe read can be performed with respect to bins 0 through 3. Finally, a third strobe read can be performed with respect to bins 0 through 3. The data obtained from the strobe reads performed with respect to each of the bins 0 through 3 can be combined to obtain final read data that is sent back to the memory sub-system controller.

[0136] A similar process can be performed for 4-bit BMCR. For example, as described above, sixteen bins can be defined with 4-bit information (“bin 0” through “bin 15”). A first strobe read can be performed with respect to bins 0 through 15. Then, a second strobe read can be performed with respect to bins 0 through 15. Finally, a third strobe read

can be performed with respect to bins 0 through 15. The data obtained from the strobe reads performed with respect to each of the bins 0 through 15 can be combined to obtain final read data that is sent back to the memory sub-system controller.

[0137] FIG. 8 illustrates an example machine of a computer system **800** within which a set of instructions, for causing the machine to perform any one or more of the methodologies discussed herein, can be executed. In some embodiments, the computer system **800** can correspond to a host system (e.g., the host system **120** of FIG. 1A) that includes, is coupled to, or utilizes a memory sub-system (e.g., the memory sub-system **110** of FIG. 1A) or can be used to perform the operations of a controller (e.g., to execute an operating system to perform operations corresponding to the CR component **137** of FIG. 1A). In alternative embodiments, the machine can be connected (e.g., networked) to other machines in a LAN, an intranet, an extranet, and/or the Internet. The machine can operate in the capacity of a server or a client machine in client-server network environment, as a peer machine in a peer-to-peer (or distributed) network environment, or as a server or a client machine in a cloud computing infrastructure or environment.

[0138] The machine can be a personal computer (PC), a tablet PC, a set-top box (STB), a Personal Digital Assistant (PDA), a memory cellular telephone, a web appliance, a server, a network router, a switch or bridge, or any machine capable of executing a set of instructions (sequential or otherwise) that specify actions to be taken by that machine. Further, while a single machine is illustrated, the term “machine” shall also be taken to include any collection of machines that individually or jointly execute a set (or multiple sets) of instructions to perform any one or more of the methodologies discussed herein.

[0139] The example computer system **800** includes a processing device **802**, a main memory **804** (e.g., read-only memory (ROM), flash memory, dynamic random access memory (DRAM) such as synchronous DRAM (SDRAM) or RDRAM, etc.), a static memory **806** (e.g., flash memory, static random access memory (SRAM), etc.), and a data storage system **818**, which communicate with each other via a bus **830**.

[0140] Processing device **802** represents one or more general-purpose processing devices such as a microprocessor, a central processing unit, or the like. More particularly, the processing device can be a complex instruction set computing (CISC) microprocessor, reduced instruction set computing (RISC) microprocessor, very long instruction word (VLIW) microprocessor, or a processor implementing other instruction sets, or processors implementing a combination of instruction sets. Processing device **802** can also be one or more special-purpose processing devices such as an application specific integrated circuit (ASIC), a field programmable gate array (FPGA), a digital signal processor (DSP), network processor, or the like. The processing device **802** is configured to execute instructions **826** for performing the operations and steps discussed herein. The computer system **800** can further include a network interface device **808** to communicate over the network **820**.

[0141] The data storage system **818** can include a machine-readable storage medium **824** (also known as a computer-readable medium) on which is stored one or more sets of instructions **826** or software embodying any one or more of the methodologies or functions described herein.

The instructions **826** can also reside, completely or at least partially, within the main memory **804** and/or within the processing device **802** during execution thereof by the computer system **800**, the main memory **804** and the processing device **802** also constituting machine-readable storage media. The machine-readable storage medium **824**, data storage system **818**, and/or main memory **804** can correspond to the memory sub-system **110** of FIG. 1A.

[0142] In one embodiment, the instructions **826** include instructions to implement functionality corresponding to a CR component (e.g., the CR component **137** of FIG. 1A). While the machine-readable storage medium **824** is shown in an example embodiment to be a single medium, the term “machine-readable storage medium” should be taken to include a single medium or multiple media that store the one or more sets of instructions. The term “machine-readable storage medium” shall also be taken to include any medium that is capable of storing or encoding a set of instructions for execution by the machine and that cause the machine to perform any one or more of the methodologies of the present disclosure. The term “machine-readable storage medium” shall accordingly be taken to include, but not be limited to, solid-state memories, optical media, and magnetic media.

[0143] Some portions of the preceding detailed descriptions have been presented in terms of algorithms and symbolic representations of operations on data bits within a computer memory. These algorithmic descriptions and representations are the ways used by those skilled in the data processing arts to most effectively convey the substance of their work to others skilled in the art. An algorithm is here, and generally, conceived to be a self-consistent sequence of operations leading to a desired result. The operations are those requiring physical manipulations of physical quantities. Usually, though not necessarily, these quantities take the form of electrical or magnetic signals capable of being stored, combined, compared, and otherwise manipulated. It has proven convenient at times, principally for reasons of common usage, to refer to these signals as bits, values, elements, symbols, characters, terms, numbers, or the like.

[0144] It should be borne in mind, however, that all of these and similar terms are to be associated with the appropriate physical quantities and are merely convenient labels applied to these quantities. The present disclosure can refer to the action and processes of a computer system, or similar electronic computing device, that manipulates and transforms data represented as physical (electronic) quantities within the computer system’s registers and memories into other data similarly represented as physical quantities within the computer system memories or registers or other such information storage systems.

[0145] The present disclosure also relates to an apparatus for performing the operations herein. This apparatus can be specially constructed for the intended purposes, or it can include a general purpose computer selectively activated or reconfigured by a computer program stored in the computer. Such a computer program can be stored in a computer readable storage medium, such as any type of disk including floppy disks, optical disks, CD-ROMs, and magnetic-optical disks, read-only memories (ROMs), random access memories (RAMs), EPROMs, EEPROMs, magnetic or optical cards, or any type of media suitable for storing electronic instructions, each coupled to a computer system bus.

[0146] The algorithms and displays presented herein are not inherently related to any particular computer or other

apparatus. Various general purpose systems can be used with programs in accordance with the teachings herein, or it can prove convenient to construct a more specialized apparatus to perform the method. The structure for a variety of these systems will appear as set forth in the description below. In addition, the present disclosure is not described with reference to any particular programming language. It will be appreciated that a variety of programming languages can be used to implement the teachings of the disclosure as described herein.

[0147] The present disclosure can be provided as a computer program product, or software, that can include a machine-readable medium having stored thereon instructions, which can be used to program a computer system (or other electronic devices) to perform a process according to the present disclosure. A machine-readable medium includes any mechanism for storing information in a form readable by a machine (e.g., a computer). In some embodiments, a machine-readable (e.g., computer-readable) medium includes a machine (e.g., a computer) readable storage medium such as a read only memory (“ROM”), random access memory (“RAM”), magnetic disk storage media, optical storage media, flash memory components, etc.

[0148] In the foregoing specification, embodiments of the disclosure have been described with reference to specific example embodiments thereof. It will be evident that various modifications can be made thereto without departing from the broader spirit and scope of embodiments of the disclosure as set forth in the following claims. The specification and drawings are, accordingly, to be regarded in an illustrative sense rather than a restrictive sense.

What is claimed is:

1. A memory device comprising:
 - a memory array; and
 - control logic, operatively coupled with the memory array, to perform operations comprising:
 - identifying a target cell of the memory array, wherein the target cell is associated with a read operation; and
 - assigning the target cell to a state information bin, wherein the state information bin defines a boost voltage level offset.
2. The memory device of claim 1, wherein assigning the target cell to the state information bin further comprises identifying the state information bin based on cell state information for a group of cells adjacent to the target cell.
3. The memory device of claim 2, wherein the group of cells comprises a single cell, and wherein the cell state information comprises at least one of: 1-bit information or 2-bit information.
4. The memory device of claim 2, wherein the group of cells comprises a first cell and a second cell, and wherein the cell state information comprises at least one of: 1-bit information obtained for the first cell and 1-bit information obtained for the second cell, or 2-bit information obtained for the first cell and 2-bit information obtained for the second cell.
5. The memory device of claim 1, wherein the operations further comprise causing the target cell to be read using the boost voltage level offset.
6. The memory device of claim 5, wherein causing the target cell to be read using the boost voltage level offset comprises:
 - performing a first strobe read with respect to the state information bin; and

after performing the first strobe read, performing a second strobe read with respect to the state information bin.

7. The memory device of claim 1, wherein the state information bin corresponds to a threshold voltage sub-distribution of target cells comprising the target cell.

8. A memory device comprising:

a memory array comprising a target cell associated with a read operation, and a group of cells adjacent to the target cell; and

control logic, operatively coupled with the memory array, to perform operations comprising:

assigning the target cell to a state information bin based on cell state information for the group of cells, wherein the state information bin defines a boost voltage level offset; and

causing the target cell to be read using the boost voltage level offset.

9. The memory device of claim 8, wherein the group of cells comprises a single cell.

10. The memory device of claim 9, wherein the cell state information comprises at least one of: 1-bit information or 2-bit information.

11. The memory device of claim 8, wherein the group of cells comprises a first cell and a second cell.

12. The memory device of claim 11, wherein the cell state information comprises at least one of: 1-bit information obtained for the first cell and 1-bit information obtained for the second cell, or 2-bit information obtained for the first cell and 2-bit information obtained for the second cell.

13. The memory device of claim 8, wherein causing the target cell to be read using the boost voltage level offset comprises:

performing a first strobe read with respect to the state information bin; and

after performing the first strobe read, performing a second strobe read with respect to the state information bin.

14. The memory device of claim 8, wherein the state information bin corresponds to a threshold voltage sub-distribution of target cells comprising the target cell.

15. A memory device comprising:

a memory array comprising a target cell associated with a read operation; and

control logic, operatively coupled with the memory array, to perform operations comprising:

receiving cell state information for a group of cells adjacent to the target cell;

identifying a state information bin for the target cell based on the cell state information, wherein the state information bin defines a boost voltage level offset and corresponds to a threshold voltage sub-distribution of target cells comprising the target cell; and

causing the target cell to be read using the boost voltage level offset.

16. The memory device of claim 15, wherein the group of cells comprises a single cell.

17. The memory device of claim 16, wherein the cell state information comprises at least one of: 1-bit information or 2-bit information.

18. The memory device of claim 15, wherein the group of cells comprises a first cell and a second cell.

19. The memory device of claim 18, wherein the cell state information at least one of: 1-bit information obtained for the first cell and 1-bit information obtained for the second

cell, or 2-bit information obtained for the first cell and 2-bit information obtained for the second cell.

20. The memory device of claim **15**, wherein causing the target cell to be read using the boost voltage level offset comprises:

performing a first strobe read with respect to the state information bin; and

after performing the first strobe read, performing a second strobe read with respect to the state information bin.

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